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M16C/30P Group SINGLE-CHIP 16-BIT CMOS MICROCOMPUTER

REJ03B0088-0122 Rev.1.22 Mar 30, 2007

1. **Overview**

The M16C/30P Group of single-chip microcomputers is built using the high-performance silicon gate CMOS process using a M16C/60 Series CPU core and is packaged in a 100-pin plastic molded QFP.

These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed. In addition, these microcomputers contain a multiplier and DMAC which combined with fast instruction processing capability, make it suitable for control of various OA, communication, and industrial equipment which requires high-speed arithmetic/ logic operations.

1.1 **Applications**

Audio, cameras, TV, home appliance, office/communications/portable/industrial equipment, etc.

1.2 **Performance Outline**

Table 1.1 lists Performance Outline of M16C/30P Group.

Table 1.1 Performance Outline of M16C/30P Group

	Item	Performance
CPU	Number of Basic Instructions	
	Minimum Instruction	62.5ns(f(XIN)=16MHz, VCC1=VCC2=3.0 to 5.5V, no wait)
	Execution Time	100ns(f(XIN)=10MHz, VCC1=VCC2=2.7 to 5.5V, no wait)
	Operation Mode	Single-chip, memory expansion and microprocessor
		mode
	Memory Space	1 Mbyte
	Memory Capacity	See Table 1.2 Product List
Peripheral	Port	Input/Output: 87 pins, Input: 1 pin
Function	Multifunction Timer	Timer A: 16 bits x 3 channels,
		Timer B: 16 bits x 3 channels
	Serial Interface	1 channels
		Clock synchronous, UART, I ² CBus ⁽¹⁾ , IEBus ⁽²⁾
		2 channels
		Clock synchronous, UART, I ² CBus ⁽¹⁾
	A/D Converter	10-bit A/D converter: 1 circuit, 18 channels
	DMAC	2 channels
	CRC Calculation Circuit	CCITT-CRC
	Watchdog Timer	15 bits x 1 channel (with prescaler)
	Interrupt	Internal: 20 sources, External: 7 sources, Software: 4
		sources, Priority level: 7 levels
	Clock Generating Circuit	2 circuits
		Main clock generation circuit (*),
		Subclock generation circuit (*),
		(*)Equipped with a built-in feedback resistor.
Electric	Supply Voltage	VCC1=VCC2=3.0 to 5.5 V (f(XIN)=16MHz)
Characteristics		VCC1=VCC2=2.7 to 5.5 V (f(XIN)=10MHz, no wait)
	Power Consumption	10 mA (VCC1=VCC2=5V, f(XIN)=16MHz)
		8 mA (VCC1=VCC2=3V, f(XIN)=10MHz)
		1.8 μA (VCC1=VCC2=3V, f(XCIN)=32kHz, wait mode)
		0.7 μA(VCC1=VCC2=3V, stop mode)
One time flash version	Program Supply Voltage	3.3±0.3 V or 5.0±0.5 V
Flash memory version	Program/Erase Supply Voltage	3.3±0.3 V or 5.0±0.5 V
	Program and Erase Endurance	100 times (all area)
Operating Ambi	ent Temperature	-20 to 85°C, -40 to 85°C
Package		100-pin plastic mold QFP, LQFP
		<u> </u>

- 1. I^2C bus is a registered trademark of Koninklijke Philips Electronics N. V.
- 2. IEBus is a registered trademark of NEC Electronics Corporation.
- 3. Use the M16C/30P on VCC1 = VCC2.

1.3 Block Diagram

Figure 1.1 is a M16C/30P Group Block Diagram.

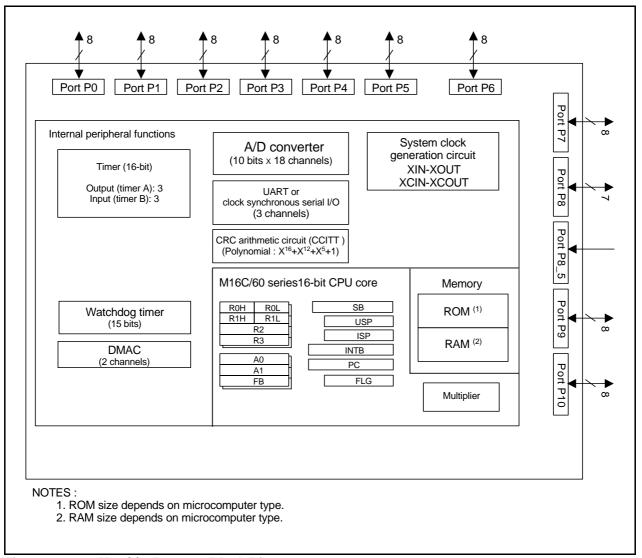


Figure 1.1 M16C/30P Group Block Diagram

1.4 Product List

Table 1.2 lists the M16C/30P group products and Figure 1.2 shows the Part No., Memory Size, and Package. Table 1.4 lists Product Code of MASK ROM version for M16C/30P. Figure 1.3 shows the Marking Diagram of Mask ROM Version for M16C/30P (Top View). Table 1.5 lists Product Code of One Time Flash version, Flash Memory version, and ROM-less version for M16C/30P. Figure 1.4 shows the Marking Diagram of One Time Flash version, Flash Memory version, and ROM-less Version for M16C/30P (Top View). Please specify the marking for M16C30P (MASK ROM version) when placing an order for ROM.

Table 1.2 Product List (1)

As of March 2007

	110 to 11							
Part No.		ROM Capacity	RAM Capacity	package code (1)	Remarks			
M30302MAP-XXXFP		96 Kbytes	5 Kbytes	PRQP0100JB-A	Mask ROM version			
M30302MAP-XXXGP				PLQP0100KB-A				
M30302MCP-XXXFP		128 Kbytes		PRQP0100JB-A				
M30302MCP-XXXGP				PLQP0100KB-A				
M30302MDP-XXXFP		160 Kbytes	6 Kbytes	PRQP0100JB-A				
M30302MDP-XXXGP				PLQP0100KB-A				
M30302MEP-XXXFP		192 Kbytes		PRQP0100JB-A				
M30302MEP-XXXGP				PLQP0100KB-A				
M30302GAPFP		96 Kbytes	5 Kbytes	PRQP0100JB-A	One Time Flash			
M30302GAPGP	(D)			PLQP0100KB-A	version (blank product)			
M30302GCPFP		128 Kbytes		PRQP0100JB-A	(Sidilit product)			
M30302GCPGP	(D)			PLQP0100KB-A				
M30302GDPFP		160 Kbytes	6 Kbytes	PRQP0100JB-A				
M30302GDPGP	(D)			PLQP0100KB-A				
M30304GDPFP	(D)	=	12 Kbytes	PRQP0100JB-A				
M30304GDPGP	(D)			PLQP0100KB-A				
M30302GEPFP		192 Kbytes	6 Kbytes	PRQP0100JB-A				
M30302GEPGP	(D)			PLQP0100KB-A				
M30304GEPFP	(D)	1	12 Kbytes	PRQP0100JB-A				
M30304GEPGP	(D)			PLQP0100KB-A				
M30302GGPFP	(D)	256 Kbytes	12 Kbytes	PRQP0100JB-A				
M30302GGPGP	(D)	1		PLQP0100KB-A				
M30302GAP-XXXFP		96 Kbytes	5 Kbytes	PRQP0100JB-A	One Time Flash			
M30302GAPvGP	(D)	1		PLQP0100KB-A	version (factory programmed			
M30302GCP-XXXFP		128 Kbytes		PRQP0100JB-A	product)			
M30302GCP-XXXGP	(D)			PLQP0100KB-A				
M30302GDP-XXXFP		160 Kbytes	6 Kbytes	PRQP0100JB-A				
M30302GDP-XXXGP	(D)	1		PLQP0100KB-A				
M30304GDP-XXXFP	(D)	1	12 Kbytes	PRQP0100JB-A				
M30304GDP-XXXGP	(D)	1		PLQP0100KB-A				
M30302GEP-XXXFP		192 Kbytes	6 Kbytes	PRQP0100JB-A				
M30302GEP-XXXGP	(D)	1		PLQP0100KB-A				
M30304GEP-XXXFP	(D)	1	12 Kbytes	PRQP0100JB-A				
M30304GEP-XXXGP	(D)	1		PLQP0100KB-A				
M30302GGP-XXXFP	(D)	256 Kbytes	12 Kbytes	PRQP0100JB-A				
M30302GGP-XXXGP	(D)	1		PLQP0100KB-A				
				•				

(D): Under development

(P): Under planning

NOTES:

1. Previous package codes are as follows.

PRQP0100JB-A: 100P6S-A, PLQP0100KB-A: 100P6Q-A

2. Block A (4-Kbytes space) is available in flash memory version.

Page 4 of 53

Table 1.3 Product List (2)

As of March 2007

Part No.	ROM Capacity	RAM Capacity	package code (1)	Remarks
M30302FAPFP	96 K + 4 Kbytes	5 Kbytes	PRQP0100JB-A	Flash memory
M30302FAPGP			PLQP0100KB-A	version ⁽²⁾
M30302FCPFP	128 K + 4 Kbytes		PRQP0100JB-A	
M30302FCPGP			PLQP0100KB-A	
M30302FEPFP	192 K + 4 Kbytes	6 Kbytes	PRQP0100JB-A	
M30302FEPGP	-		PLQP0100KB-A	
M30302SPFP	-	6 Kbytes	PRQP0100JB-A	ROM-less version
M30302SPGP			PLQP0100KB-A	

(D): Under development(P): Under planning

NOTES:

1. Previous package codes are as follows.

PRQP0100JB-A: 100P6S-A, PLQP0100KB-A: 100P6Q-A

2. Block A (4-Kbytes space) is available in flash memory version.

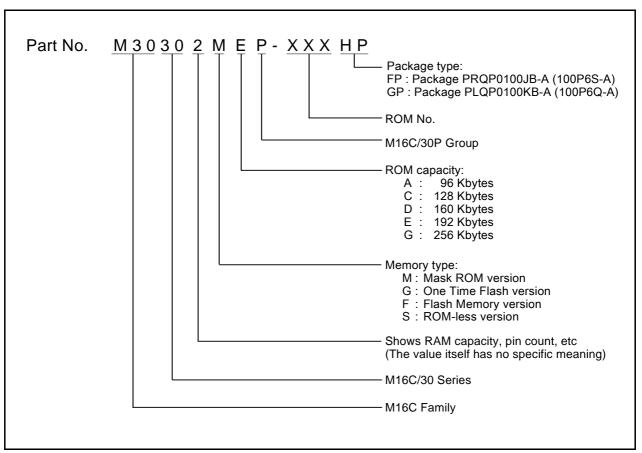


Figure 1.2 Part No., Memory Size, and Package

Page 5 of 53

Table 1.4 Product Code of MASK ROM version for M16C/30P

Product Code	Package	Operating Ambient Temperature
U1	Lead-free	-20°C to 85°C
U4		-40°C to 85°C

PRQP0100JB-A (100P6S-A) 1. Standard Renesas Mark M 1 6 C M30302MDP - XXXFP Part No. (See Figure 1.2 Part No., Memory Size, and Package) A U1 XXXXXXX Chip version, product code and date code : Shows chip version. Henceforth, whenever it changes a version, O it continues with A, B, and C. : Shows Product code. (See table 1.3 Product Code) XXXXXXX : Seven digits 2. Customer's Parts Number + Renesas catalog name M30302MDP - XXXFP Part No. (See Figure 1.2 Part No., Memory Size, and Package) Α U 1 Chip version and product code : Shows chip version. M16C XXXXXX Henceforth, whenever it changes a version, it continues with A, B, and C. : Shows Product code. (See table 1.3 Product Code) U1 Date code seven digits PLQP0100KB-A (100P6Q-A) 1. Standard Renesas Mark M16C M30302MDP Part No. (See Figure 1.2 Part No., Memory Size, and Package) - XXXGP A U1 XXXXXXX Chip version, product code and date code : Shows chip version. Henceforth, whenever it changes a version, O it continues with A, B, and C. : Shows Product code. (See table 1.3 Product Code) XXXXXXX: Seven digits 2. Customer's Parts Number + Renesas catalog name - Part No. (See Figure 1.2 Part No., Memory Size, and Package) M30302MDP A U 1 - XXXGP Chip version and product code : Shows chip version. M16C XXXXXXX Henceforth, whenever it changes a version, it continues with A, B, and C. U1 : Shows Product code. (See table 1.3 Product Code) Date code seven digits

Figure 1.3 Marking Diagram of Mask ROM Version for M16C/30P (Top View)

1. Refer to the mark specification form for details of the Mask ROM version marking.

Table 1.5 Product Code of One Time Flash version, Flash Memory version, and ROM-less version for M16C/30P

			Interna	Operating	
	Product Code	Package	Program and Erase Endurance	Temperature Range	Operating Ambient Temperature
One Time Flash	U3	Lead-	0	0°C to 60°C	-40°C to 85°C
version	U5	free			-20°C to 85°C
Flash Memory	U3	Lead-	100	0°C to 60°C	-40°C to 85°C
version	U5	free			-20°C to 85°C
ROM-less version	U3	Lead-	-	-	-40°C to 85°C
	U5	free			-20°C to 85°C

NOTES: The one time flash version can be written once only.

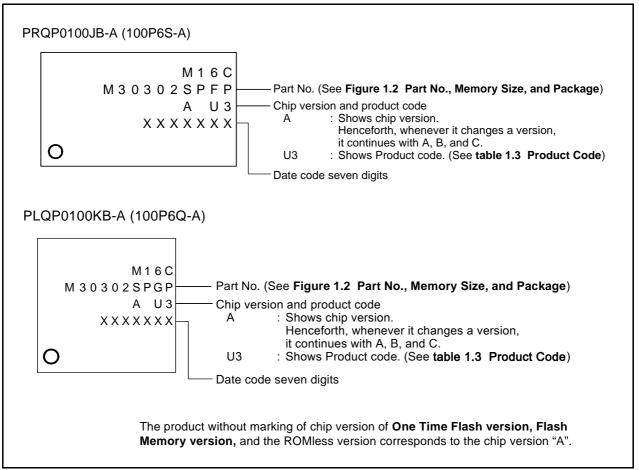


Figure 1.4 Marking Diagram of One Time Flash version, Flash Memory version, and ROM-less Version for M16C/30P (Top View)

Page 7 of 53

1.5 Pin Configuration

Figures 1.5 to 1.6 show the pin configurations (top view).

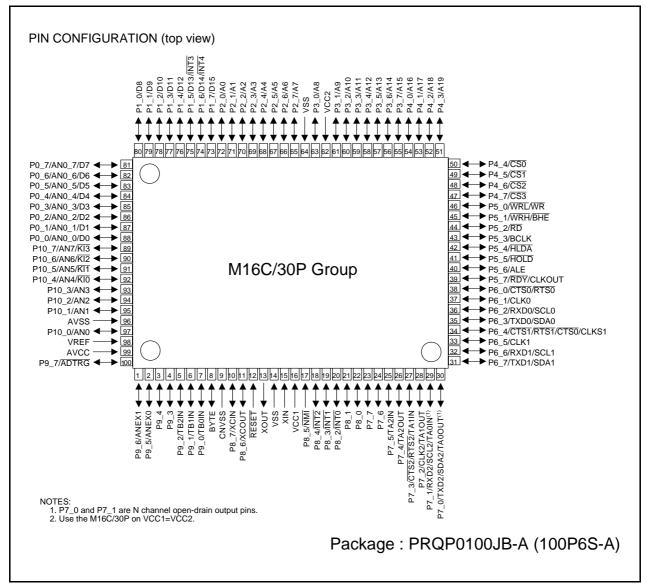


Figure 1.5 Pin Configuration (Top View)

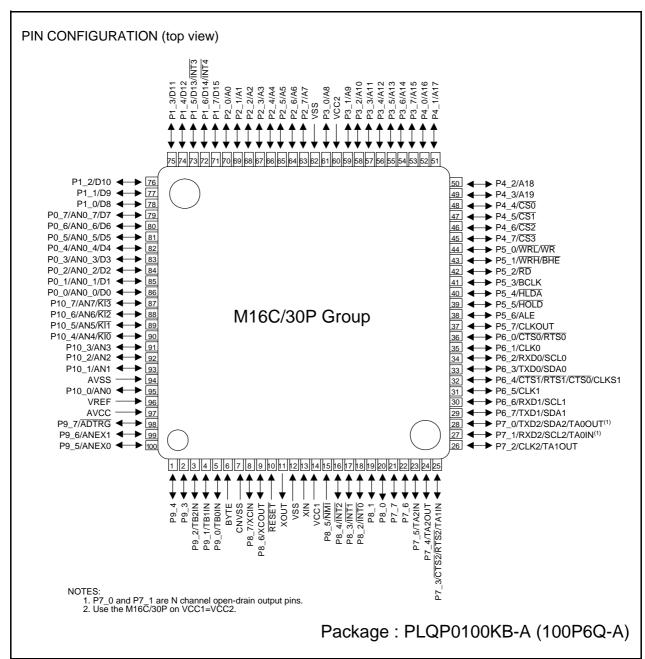


Figure 1.6 Pin Configuration (Top View)

Pin Characteristics (1) Table 1.6

Iabi	U 1.0	1 111 \	Jilai aci	eristics (1)				
Pin FP	No. GP	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
1	99		P9_6				ANEX1	
2	100		P9_5				ANEX0	
3	1		P9_4				ANEXO	
4	2		P9_3					
5	3		P9_2		TB2IN			
6	4		P9_1		TB1IN			
7	5		P9_0		TB0IN			
8	6	BYTE			-			
9	7	CNVSS						
10	8	XCIN	P8_7					
11	9	XCOUT	P8_6					
12	10	RESET						
13	11	XOUT						
14	12	VSS						
15	13	XIN						
16	14	VCC1						
17	15		P8_5	NMI				
18	16		P8_4	ĪNT2				
19	17		P8_3	ĪNT1				
20	18		P8_2	ĪNT0				
21	19		P8_1					
22	20		P8_0					
23	21		P7_7					
24	22		P7_6					
25	23		P7_5		TA2IN			
26	24		P7_4		TA2OUT			
27	25		P7_3		TA1IN	CTS2/RTS2		
28	26		P7_2		TA1OUT	CLK2		
29	27		P7_1		TA0IN	RXD2/SCL2		
30	28		P7_0		TA0OUT	TXD2/SDA2		
31	29		P6_7			TXD1/SDA1		
32	30		P6_6			RXD1/SCL1		
33	31		P6_5			CLK1		
34	32		P6_4			CTS1/RTS1/CTS0/CLKS1		
35	33		P6_3			TXD0/SDA0		
36	34		P6_2			RXD0/SCL0		
37	35		P6_1			CLK0		
38	36	-	P6_0			CTS0/RTS0		
39	37		P5_7					RDY/CLKOUT
40	38		P5_6					ALE
41	39		P5_5					HOLD
42	40		P5_4					HLDA
43	41		P5_3					BCLK
44	42		P5_2					RD
45	43		P5_1					WRH/BHE
46	44		P5_0					WRL/WR
47	45		P4_7					CS3
48	46		P4_6					CS2
49	47		P4_5					CS1
50	48		P4_4					CS0

Table 1.7 Pin Characteristics (2)

Iabi				eristics (2)				
	No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP		D4 0					A19
51 52	49 50		P4_3 P4_2					A19
								A17
53	51		P4_1					
54	52		P4_0					A16
55	53		P3_7					A15
56	54		P3_6					A14
57	55 56		P3_5					A13 A12
58 59	57		P3_4 P3_3					A12
60	58		P3_3 P3_2					A10
61	59		P3_2 P3_1					A9
62	60	VCC2	F3_1					A9
63	61	V002	P3_0					A8
64	62	VSS	1 0_0					7.0
65	63		P2_7					A7
66	64		P2_6					A6
67	65		P2_5					A5
68	66		P2_4					A4
69	67		P2_3					A3
70	68		P2_2					A2
71	69		P2_1					A1
72	70		P2_0					A0
73	71		P1_7					D15
74	72		P1_6	ĪNT4				D14
75	73		P1_5	ĪNT3				D13
76	74		P1_4					D12
77	75		P1_3					D11
78	76		P1_2					D10
79	77		P1_1					D9
80	78		P1_0					D8
81	79		P0_7				AN0_7	D7
82	80		P0_6				AN0_6	D6
83	81		P0_5				AN0_5	D5
84	82		P0_4				AN0_4	D4
85	83		P0_3				AN0_3	D3
86	84		P0_2				AN0_2	D2
87	85		P0_1				AN0_1	D1
88	86		P0_0				AN0_0	D0
89	87		P10_7	KI3			AN7	
90	88		P10_6	KI2			AN6	
91	89		P10_5	KI2 KI1			AN5	
92	90			KII				
			P10_4	KIU			AN4	
93	91 92		P10_3 P10_2				AN3 AN2	
94 95	93		P10_2 P10_1	-			AN2 AN1	
96	93	AVSS	1.10_1				AINI	
97	95	7.1000	P10_0	+			ANO	
98	96	VREF					7	
99	97	AVCC						
		7,00	D0 =				ADTE C	
100	98		P9_7				ADTRG	

1.6 Pin Description

Table 1.8 Pin Description (1)

Signal Name	Pin Name	I/O Type	Description
Power supply input	VCC1, VCC2 VSS	1	Apply 2.7 to 5.5 V to the VCC1 and VCC2 pins and 0 V to the Vss pin. The VCC apply condition is that VCC1 = VCC2.
Analog power supply input	AVCC AVSS	I	Applies the power supply for the A/D converter. Connect the AVCC pin to VCC1. Connect the AVSS pin to VSS.
Reset input	RESET	I	The microcomputer is in a reset state when applying "L" to the this pin.
CNVSS	CNVSS	I	Switches processor mode. Connect this pin to VSS to when after a reset to start up in single-chip mode. Connect this pin to VCC1 to start up in microprocessor mode.
External data bus width select input	BYTE	I	Switches the data bus in external memory space. The data bus is 16 bits long when the this pin is held "L" and 8 bits long when the this pin is held "H". Set it to either one. Connect this pin to VSS when an single-chip mode.
Bus control pins	D0 to D7	I/O	Inputs and outputs data (D0 to D7) when these pins are set as the separate bus.
	D8 to D15	I/O	Inputs and outputs data (D8 to D15) when external 16-bit data bus is set as the separate bus.
	A0 to A19	0	Output address bits (A0 to A19).
	CS0 to CS3	0	Output CS0 to CS3 signals. CS0 to CS3 are chip-select signals to specify an external space.
	WRL/WR WRH/BHE RD	0	Output WRL, WRH, (WR, BHE), RD signals. WRL and WRH or BHE and WR can be switched by program. • WRL, WRH and RD are selected The WRL signal becomes "L" by writing data to an even address in an external memory space. The WRH signal becomes "L" by writing data to an odd address in an external memory space. The RD pin signal becomes "L" by reading data in an external memory space. • WR, BHE and RD are selected The WR signal becomes "L" by writing data in an external memory space. The RD signal becomes "L" by writing data in an external memory space. The RD signal becomes "L" by reading data in an external memory space. The BHE signal becomes "L" by accessing an odd address. Select WR, BHE and RD for an external 8-bit data bus.
	ALE	0	ALE is a signal to latch the address.
	HOLD	Ι	While the HOLD pin is held "L", the microcomputer is placed in a hold state.
	HLDA	0	In a hold state, HLDA outputs a "L" signal.
	RDY	I	While applying a "L" signal to the RDY pin, the microcomputer is placed in a wait state.

I : Input O : Output I/O : Input and output

Pin Description (2) Table 1.9

Table 1.9	Fili Description	(2)	
Signal Name	Pin Name	I/O Type	Description
Main clock	XIN	I	I/O pins for the main clock generation circuit. Connect a ceramic
input			resonator or crystal oscillator between XIN and XOUT. To use the
Main clock	XOUT	0	external clock, input the clock from XIN and leave XOUT open.
output	VOIN		I/O mine for a sub-plant and illustration size if O and a sub-plant and illustration
Sub clock input	XCIN	I	I/O pins for a sub clock oscillation circuit. Connect a crystal oscillator between XCIN and XCOUT. To use the external clock, input the clock
Sub clock	XCOUT	0	from XCIN and leave XCOUT open.
output	7,0001		
Clock output	CLKOUT	0	The clock of the same cycle as fC, f8, or f32 is outputted.
INT interrupt	INT0 to INT4	ı	Input pins for the INT interrupt.
input			I mpet pine is the min menaph
NMI interrupt	NMI	I	Input pin for the NMI interrupt.
input			
Key input	KI0 to KI3	I	Input pins for the key input interrupt.
interrupt input			
Timer A	TA0OUT to	I/O	These are timer A0 to timer A2 I/O pins. (however, the output of
	TA2OUT		TA0OUT for the N-channel open drain output.)
	TA0IN to TA2IN	<u> </u>	These are timer A0 to timer A2 input pins.
Timer B	TB0IN to TB2IN	l	These are timer B0 to timer B2 input pins.
Serial interface	CTS0 to CTS2	I	These are send control input pins.
interiace	RTS0 to RTS2	0	These are receive control output pins.
	CLK0 to CLK2	I/O	These are transfer clock I/O pins.
	RXD0 to RXD2	1	These are serial data input pins.
	TXD0 to TXD2	0	These are serial data output pins. (however, TXD2 for the N-channel
		_	open drain output.)
.0.5	CLKS1	0	This is output pin for transfer clock output from multiple pins function.
I ² C mode	SDA0 to SDA2	I/O	These are serial data I/O pins. (however, SDA2 for the N-channel open drain output.)
	SCL0 to SCL2	I/O	These are transfer clock I/O pins. (however, SCL2 for the N-channel
	SCLO 10 SCL2	1/0	open drain output.)
Reference	VREF	I	Applies the reference voltage for the A/D converter.
voltage input			, in the second
A/D converter	AN0 to AN7,	I	Analog input pins for the A/D converter.
	AN0_0 to AN0_7		
	ADTRG	I	This is an A/D trigger input pin.
	ANEX0	I/O	This is the extended analog input pin for the A/D converter, and is the
			output in external op-amp connection mode.
	ANEX1	I	This is the extended analog input pin for the A/D converter.
I/O port	P0_0 to P0_7,	I/O	8-bit I/O ports in CMOS, having a direction register to select an input
	P1_0 to P1_7, P2_0 to P2_7,		or output. Each pin is set as an input port or output port. An input port can be set
	P3_0 to P3_7,		for a pull-up or for no pull-up in 4-bit unit by program. (however, P7_0
	P4_0 to P4_7,		and P7_1 for the N-channel open drain output.)
	P5_0 to P5_7,		_ ' ' '
	P6_0 to P6_7,		
	P7_0 to P7_7,		
	P9_0 to P9_7,		
	P9_0 to P9_7, P10_0 to P10_7	1/0	NO seeds hereign a service lead for setime to 20
	P9_0 to P9_7, P10_0 to P10_7 P8_0 to P8_4,	I/O	I/O ports having equivalent functions to P0.
Input port	P9_0 to P9_7, P10_0 to P10_7	I/O	I/O ports having equivalent functions to P0. Input pin for the NMI interrupt. Pin states can be read by the P8_5 bit

I : Input O : Output I/O : Input and output



Central Processing Unit (CPU) 2.

Figure 2.1 shows the CPU registers. The CPU has 13 registers. Of these, R0, R1, R2, R3, A0, A1 and FB comprise a register bank. There are two register banks.

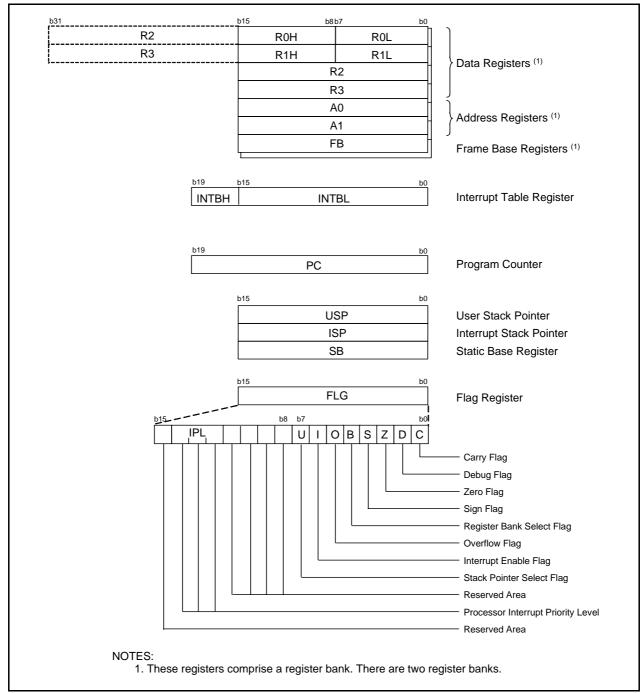


Figure 2.1 **Central Processing Unit Register**

2.1 Data Registers (R0, R1, R2 and R3)

The R0 register consists of 16 bits, and is used mainly for transfers and arithmetic/logic operations. R1 to R3 are the same as R0.

The R0 register can be separated between high (R0H) and low (R0L) for use as two 8-bit data registers.

R1H and R1L are the same as R0H and R0L. Conversely, R2 and R0 can be combined for use as a 32-bit data register (R2R0). R3R1 is the same as R2R0.

2.2 Address Registers (A0 and A1)

The register A0 consists of 16 bits, and is used for address register indirect addressing and address register relative addressing. They also are used for transfers and logic/logic operations. A1 is the same as A0. In some instructions, registers A1 and A0 can be combined for use as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is configured with 16 bits, and is used for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is configured with 20 bits, indicating the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is configured with 20 bits, indicating the address of an instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

Stack pointer (SP) comes in two types: USP and ISP, each configured with 16 bits. Your desired type of stack pointer (USP or ISP) can be selected by the U flag of FLG.

2.7 Static Base Register (SB)

SB is configured with 16 bits, and is used for SB relative addressing.

2.8 Flag Register (FLG)

FLG consists of 11 bits, indicating the CPU status.

2.8.1 Carry Flag (C Flag)

This flag retains a carry, borrow, or shift-out bit that has occurred in the arithmetic/logic unit.

2.8.2 Debug Flag (D Flag)

The D flag is used exclusively for debugging purpose. During normal use, it must be set to "0".

2.8.3 Zero Flag (Z Flag)

This flag is set to "1" when an arithmetic operation resulted in 0; otherwise, it is "0".

2.8.4 Sign Flag (S Flag)

This flag is set to "1" when an arithmetic operation resulted in a negative value; otherwise, it is "0".

2.8.5 Register Bank Select Flag (B Flag)

Register bank 0 is selected when this flag is "0"; register bank 1 is selected when this flag is "1".

2.8.6 Overflow Flag (O Flag)

This flag is set to "1" when the operation resulted in an overflow; otherwise, it is "0".

2.8.7 Interrupt Enable Flag (I Flag)

This flag enables a maskable interrupt.

Maskable interrupts are disabled when the I flag is "0", and are enabled when the I flag is "1". The I flag is cleared to "0" when the interrupt request is accepted.



2.8.8 Stack Pointer Select Flag (U Flag)

ISP is selected when the U flag is "0"; USP is selected when the U flag is "1".

The U flag is cleared to "0" when a hardware interrupt request is accepted or an INT instruction for software interrupt Nos. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is configured with three bits, for specification of up to eight processor interrupt priority levels from level 0 to level 7.

If a requested interrupt has priority greater than IPL, the interrupt is enabled.

2.8.10 Reserved Area

When write to this bit, write "0". When read, its content is indeterminate.



M16C/30P Group 3. Memory

3. Memory

Figure 3.1 is a Memory Map of the M16C/30P group. The address space extends the 1 Mbyte from address 00000h to FFFFFh.

The internal ROM is allocated in a lower address direction beginning with address FFFFh. For example, a 64-Kbyte internal ROM is allocated to the addresses from F0000h to FFFFFh.

The fixed interrupt vector table is allocated to the addresses from FFFDCh to FFFFFh. Therefore, store the start address of each interrupt routine here.

The internal RAM is allocated in an upper address direction beginning with address 00400h. For example, a 5-Kbyte internal RAM is allocated to the addresses from 00400h to 017FFh. In addition to storing data, the internal RAM also stores the stack used when calling subroutines and when interrupts are generated. The SFR is allocated to the addresses from 00000h to 003FFh. Peripheral function control registers are located here. Of the SFR, any area which has no functions allocated is reserved for future use and cannot be used by users.

The special page vector table is allocated to the addresses from FFE00h to FFFDBh. This vector is used by the JMPS or JSRS instruction. For details, refer to the M16C/60 and M16C/20 Series Software Manual.

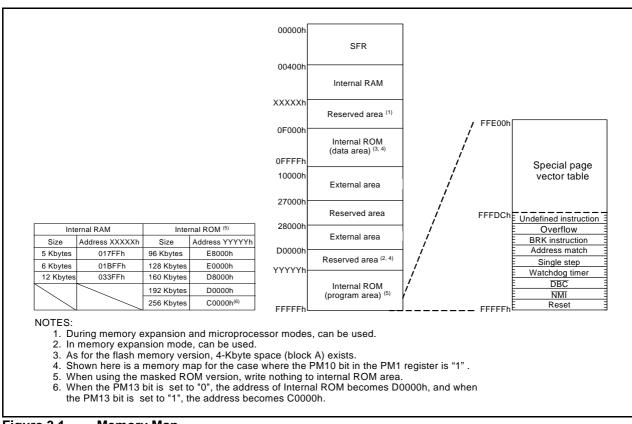


Figure 3.1 Memory Map

Special Function Register (SFR) 4.

SFR(Special Function Register) is the control register of peripheral functions. Tables 4.1 to 4.5 list the SFR information.

SFR Information (1) (1) Table 4.1

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0 (2)	PM0	00000000b(CNVSS pin is "L") 00000011b(CNVSS pin is "H")
0005h	Processor Mode Register 1	PM1	00XXX0X0b
0006h	System Clock Control Register 0	CM0	01001000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Chip Select Control Register	CSR	00000001b
0009h	Address Match Interrupt Enable Register	AIER	XXXXXX00b
0003h	Protect Register	PRCR	XX000000b
000An	1 Toteot (Yegistei	TROK	XX000000B
000Ch			
000Dh			
000Eh	Watchdog Timer Start Register	WDTS	XXh
000En		WDTS	00XXXXXXb
	Watchdog Timer Control Register		
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			X0h
0013h			
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			X0h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch			
001Dh			
001Eh			
001Fh			
0020h	DMA0 Source Pointer	SAR0	XXh
0021h			XXh
0022h			XXh
0023h			
0024h	DMA0 Destination Pointer	DAR0	XXh
0025h			XXh
0026h			XXh
0027h			
0028h	DMA0 Transfer Counter	TCR0	XXh
0029h		1.5.1.5	XXh
002Ah			70
002Bh			
002Ch	DMA0 Control Register	DM0CON	00000X00b
002Dh	2 to Control Hogistol	Divideolit	3000071000
002Eh			+
002En			+
0030h	DMA1 Source Pointer	SAR1	XXh
	Diviti Source Former	JAKI	200
0031h 0032h			XXh XXh
0032h			^^!!
0033h	DMA1 Destination Pointer	DAR1	XXh
0034n 0035h	DIMIN I DESTINATION FOUNDS	DAKT	XXh
0036h			XXh
0036h			^^!!
	LDMA1 Transfer Counter	TOD4	VVh
0038h	DMA1 Transfer Counter	TCR1	XXh
0039h			XXh
003Ah			
003Bh			
003Ch	DMA1 Control Register	DM1CON	00000X00b
003Dh			
003Eh 003Fh			

- The blank areas are reserved and cannot be accessed by users.
 The PM00 and PM01 bits do not change at software reset.
- X : Nothing is mapped to this bit



SFR Information (2) (1) Table 4.2

Address	Register	Symbol	After Reset
0040h	rregister	Зупьог	Aitel Neset
0041h			
0042h			
0043h			
0044h	INT3 Interrupt Control Register	INT3IC	XX00X000b
0045h			
0046h	UART1 BUS Collision Detection Interrupt Control Register	U1BCNIC	XXXXX000b
0047h	UARTO BUS Collision Detection Interrupt Control Register	U0BCNIC	XXXXX000b
0048h	·		
0049h	INT4 Interrupt Control Register	INT4IC	XX00X000b
004Ah	UART2 Bus Collision Detection Interrupt Control Register	BCNIC	XXXXX000b
004Bh	DMA0 Interrupt Control Register	DM0IC	XXXXX000b
004Ch	DMA1 Interrupt Control Register	DM1IC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
0050h	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	SOTIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	SORIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	SITIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	Timer A0 Interrupt Control Register	TA0IC	XXXXX000b
0056h	Timer A1 Interrupt Control Register	TA1IC	XXXXX000b
0057h	Timer A2 Interrupt Control Register	TA2IC	XXXXX000b
0058h			
0059h			
005Ah	Timer B0 Interrupt Control Register	TB0IC	XXXXX000b
005Bh	Timer B1 Interrupt Control Register	TB1IC	XXXXX000b
005Ch	Timer B2 Interrupt Control Register	TB2IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INTOIC	XX00X000b
005Eh	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Fh	INT2 Interrupt Control Register	INT2IC	XX00X000b
0060h			
to			
01AFh			
01B0h			
01B1h			
01B2h			
01B3h			
01B4h			
01B5h	Flash Memory Control Register 1 (2)	FMR1	0X00XX0Xb
01B6h			
01B7h	Flash Memory Control Register 0 (3)	FMR0	00000001b
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			
01C0h			
to			
024Fh			
0250h			
0251h			
0252h			
0253h			
0254h			
0255h			
0256h			
0257h			
0258h			
0259h			
025Ah			
025Bh			
025Ch			
		Language Control of the Control of t	
025Dh			
025Dh 025Eh	Peripheral Clock Select Register	PCLKR	00000011b
025Dh 025Eh 025Fh	Peripheral Clock Select Register	PCLKR	00000011b
025Dh 025Eh 025Fh 0260h	Peripheral Clock Select Register	PCLKR	00000011b
025Dh 025Eh 025Fh	Peripheral Clock Select Register	PCLKR	00000011b

- NOTES:
 1. The blank areas are reserved and cannot be accessed by users.
 2. This register is included in the flash memory version.
 3. This register is included in the flash memory version and one time flash version.

SFR Information (3) (1) Table 4.3

Address	Register	Symbol	After Reset
0340h	-5	-,	11 111
0341h			
0342h			
0343h			
0344h			
0345h			
0346h			
0347h			
0348h			
0349h			
0349h			
034Bh			
034Ch 034Dh			
034Eh			
034Fh			
0350h			
0351h			
0352h			
0353h			
0354h			
0355h			
0356h			
0357h			
0358h			
0359h			
035Ah			
035Bh			
035Ch			
035Dh			
035Eh	Interrupt Factor Select Register 2	IFSR2A	00XXXXXXb
035Fh	Interrupt Factor Select Register	IFSR	00h
0360h	· · · · · · · · · · · · · · · · · · ·		
0361h			
0362h			
0363h			
0364h			
0365h			
0366h			
0367h			
0368h			
0369h			
036Ah			
036Bh			
036Ch	UART0 Special Mode Register 4	LINGMBA	00h
036Dh		U0SMR4 U0SMR3	
	UARTO Special Mode Register 3		000X0X0Xb X0000000b
036Eh	UARTO Special Mode Register 2	U0SMR2	
036Fh	UARTO Special Mode Register	U0SMR	X0000000b
0370h	UART1 Special Mode Register 4	U1SMR4	00h
0371h	UART1 Special Mode Register 3	U1SMR3	000X0X0Xb
0372h	UART1 Special Mode Register 2	U1SMR2	X0000000b
0373h	UART1 Special Mode Register	U1SMR	X0000000b
0374h	UART2 Special Mode Register 4	U2SMR4	00h
0375h	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
0376h	UART2 Special Mode Register 2	U2SMR2	X0000000b
0377h	UART2 Special Mode Register	U2SMR	X0000000b
0378h	UART2 Transmit/Receive Mode Register	U2MR	00h
0379h	UART2 Bit Rate Generator	U2BRG	XXh
037Ah	UART2 Transmit Buffer Register	U2TB	XXh
037Bh			XXh
037Ch	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
037Dh	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
037Eh	UART2 Receive Buffer Register	U2RB	XXh
037Fh			XXh
			<u> </u>

NOTES:

1. The blank areas are reserved and cannot be accessed by users.

SFR Information (4) (1) Table 4.4

Address	Register	Symbol	After Reset
0380h	Count Start Flag	TABSR	000XX000b
0381h	Clock Prescaler Reset Fag	CPSRF	0XXXXXXXb
0382h	One-Shot Start Flag	ONSF	00XXX000b
0383h	Trigger Select Register	TRGSR	XXXX0000b
0384h	Up-Down Flag	UDF	XX0XX000b (2)
0385h			
0386h	Timer A0 Register	TA0	XXh
0387h			XXh
0388h	Timer A1 Register	TA1	XXh
0389h			XXh
038Ah	Timer A2 Register	TA2	XXh
038Bh	Timor 742 Register	1712	XXh
038Ch			AAII
038Dh			
038Eh			
038Fh			
0390h	Timer B0 Register	TB0	XXh
0391h			XXh
0392h	Timer B1 Register	TB1	XXh
0393h	3 ···		XXh
0394h	Timer B2 Register	TB2	XXh
0395h	Timor DE register	1.52	XXh
	L Timer AO Made Deviator	TAOMD	
0396h	Timer A0 Mode Register	TA0MR	00h
0397h	Timer A1 Mode Register	TA1MR	00h
0398h	Timer A2 Mode Register	TA2MR	00h
0399h			
039Ah			
039Bh	Timer B0 Mode Register	TB0MR	00XX0000b
039Ch	Timer B1 Mode Register	TB1MR	00XX0000b
039Dh	Timer B2 Mode Register	TB2MR	00XX0000b
039Eh	Timer bz wode rregister	TDZIVIIX	007700000
039Fh			
03A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
03A1h	UART0 Bit Rate Generator	U0BRG	XXh
03A2h	UART0 Transmit Buffer Register	U0TB	XXh
03A3h			XXh
03A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
03A5h	UARTO Transmit/Receive Control Register 1	U0C1	00000010b
03A6h	UARTO Receive Buffer Register	UORB	XXh
03A7h	Office Negation Register	OUND	XXh
	1145747	LIAME	
03A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
03A9h	UART1 Bit Rate Generator	U1BRG	XXh
03AAh	UART1 Transmit Buffer Register	U1TB	XXh
03ABh			XXh
03ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
03ADh	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
03AEh	UART1 Receive Buffer Register	U1RB	XXh
03AFh	The state of the s		XXh
03B0h	UART Transmit/Receive Control Register 2	UCON	X0000000b
03B0h	OANT HAISHII/NECEIVE COILLOI NEGISLEI Z	UUUN	70000000
03B2h			
03B3h			
03B4h			
03B5h			
03B6h			
03B7h			1
03B8h	DMA0 Request Factor Select Register	DM0SL	00h
03B9h	Divinio magazat i acion delect megiatei	DIVIOUL	0011
	DNAAA Darwaat Faataa Calaat Daristaa	DMACI	001-
03BAh	DMA1 Request Factor Select Register	DM1SL	00h
03BBh			
03BCh	CRC Data Register	CRCD	XXh
03BDh			XXh
03BEh	CRC Input Register	CRCIN	XXh
03BFh	1 -9	-	+
00Di II			

NOTES:

- The blank areas are reserved and cannot be accessed by users.
 Bit 5 in the Up-down flag is "0" by reset. However, The values in these bits when read are indeterminate.

SFR Information (5) (1) Table 4.5

Address	Register	Symbol	After Reset
03C0h	A/D Register 0	AD0	XXh
03C0H	AVD Register 0	ADO	XXh
	A/D De sister 4	1004	
03C2h	A/D Register 1	AD1	XXh
03C3h			XXh
03C4h	A/D Register 2	AD2	XXh
03C5h			XXh
03C6h	A/D Register 3	AD3	XXh
03C7h			XXh
03C8h	A/D Register 4	AD4	XXh
03C9h			XXh
03CAh	A/D Register 5	AD5	XXh
03CBh	The stage of the s	7.25	XXh
03CCh	A/D Register 6	AD6	XXh
03CDh	A/D Register 6	AD6	
	1 A /D D	457	XXh
03CEh	A/D Register 7	AD7	XXh
03CFh			XXh
03D0h			
03D1h			
03D2h			
03D3h			
03D4h	A/D Control Register 2	ADCON2	XXX000X0b
03D4H	7.75 CSOF NOGIOLOF E	7.000142	7,00007,00
	A/D Control Degister 0	ADCONO	000000000
03D6h	A/D Control Register 0	ADCON0	000X0XXXb
03D7h	A/D Control Register 1	ADCON1	00000XXXb
03D8h			
03D9h			
03DAh			
03DBh			
03DCh			
03DDh			
03DEh			
03DFh			
03E0h	Port P0 Register	P0	XXh
03E1h	Port P1 Register	P1	XXh
03E2h	Port P0 Direction Register	PD0	00h
03E3h	Port P1 Direction Register	PD1	00h
03E4h	Port P2 Register	P2	XXh
03E5h	Port P3 Register	P3	XXh
03E6h	Port P2 Direction Register	PD2	00h
03E7h	Port P3 Direction Register	PD3	00h
03E8h	Port P4 Register	P4	XXh
03E9h	Port P5 Register	P5	XXh
03EAh	Port P4 Direction Register	PD4	00h
03EBh	Port P5 Direction Register	PD5	00h
03ECh	Port P6 Register	P6	XXh
03EDh	Port P7 Register	P7	XXh
03EEh	Port P6 Direction Register	PD6	00h
03EFh	Port P7 Direction Register	PD7	00h
03F0h	Port P8 Register	P8	XXh
03F1h	Port P9 Register	P9	XXh
03F2h	Port P8 Direction Register	PD8	00X00000b
03F3h	Port P9 Direction Register	PD9	00h
03F4h	Port P10 Register	P10	XXh
03F5h			
03F6h	Port P10 Direction Register	PD10	00h
03F7h			2
03F8h			
03F9h			
03FAh			
03FBh			
03FCh	Pull-Up Control Register 0	PUR0	00h
03FDh	Pull-Up Control Register 1	PUR1	0000000b (2)
			00000010b (2)
03FEh	Pull-Up Control Register 2	PUR2	00h
03FFh	Port Control Register	PCR	00h

NOTES:

- 1. The blank areas are reserved and cannot be accessed by users.
- 2. At hardware reset, the register is as follows:

 - "00000000b" where "L" is inputted to the CNVSS pin
 "00000010b" where "H" is inputted to the CNVSS pin

At software reset, the register is as follows:

- "00000000b" where the PM01 to PM00 bits in the PM0 register are "00b" (single-chip mode).
 "00000010b" where the PM01 to PM00 bits in the PM0 register are "01b" (memory expansion mode) or "11b" (microprocessor mode).



5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol		Parameter	Condition	Rated Value	Unit
Vcc	Supply Voltage	e(VCC1=VCC2)	Vcc1=Vcc2=AVcc	-0.3 to 6.5	V
AVcc	Analog Supply	Voltage	Vcc1=Vcc2=AVcc	-0.3 to 6.5	V
Vı	Input Voltage	RESET, CNVSS, BYTE, P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, VREF, XIN		-0.3 to Vcc+0.3	V
		P7_0, P7_1		-0.3 to 6.5	V
Vo	Output Voltage	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, XOUT		-0.3 to Vcc+0.3	V
		P7_0, P7_1		-0.3 to 6.5	V
Pd	Power Dissipa	tion	-40°C <topr≤85°c< td=""><td>300</td><td>mW</td></topr≤85°c<>	300	mW
Topr	Operating Ambient	When the Microcomputer is Operating		-20 to 85 / -40 to 85	°C
	Temperature	One Time Flash Program Erase		0 to 60	
		Flash Program Erase		0 to 60	
Tstg	Storage Tempo	erature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions (1)

Current al	Parameter			Standard				
Symbol		Farameter			Max.	Unit		
Vcc	Supply Voltage (\	/cc1=Vcc2)	2.7	5.0	5.5	V		
AVcc	Analog Supply Vo	oltage		Vcc		V		
Vss	Supply Voltage			0		V		
AVss	Analog Supply Vo	oltage		0		V		
VIH	HIGH Input	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7	0.8Vcc		Vcc	V		
	Voltage	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0	0.8Vcc		Vcc	V		
		(during single-chip mode)						
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0	0.5Vcc		Vcc	V		
		(data input during memory expansion and microprocessor mode)	0.017		.,	·		
		P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, XIN, RESET, CNVSS, BYTE	0.8Vcc		Vcc	V		
		P7_0, P7_1	0.8Vcc		6.5	V		
VIL	LOW Input	P3 1 to P3 7, P4 0 to P4 7, P5 0 to P5 7	0		0.2Vcc	V		
- 1-	Voltage	P0 0 to P0 7, P1 0 to P1 7, P2 0 to P2 7, P3 0	0		0.2Vcc	V		
		(during single-chip mode)			0.2 7 00	ľ		
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0	0		0.16Vcc	V		
		(data input during memory expansion and microprocessor mode)						
		P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, XIN, RESET, CNVSS, BYTE	0		0.2Vcc	V		
IOH(peak)	HIGH Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			-10.0	mA		
IOH(avg)	HIGH Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			-5.0	mA		
IOL(peak)	LOW Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			10.0	mA		
IOL(avg)	LOW Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7			5.0	mA		
f(XIN)	Main Clock Input	VCC=3.0V to 5.5V	0		16	MHz		
	Oscillation Frequency (4)	VCC=2.7V to 3.0V	0		20×Vcc1-44	MHz		
f(XCIN)	Sub-Clock Oscilla	ation Frequency		32.768	50	kHz		
f(BCLK)	CPU Operation C	lock	0		16	MHz		

- 1. Referenced to Vcc1 = Vcc2 = 2.7 to 5.5V at $T_{opr} = -20$ to $85^{\circ}C$ / -40 to $85^{\circ}C$ unless otherwise specified.
- 2. The Average Output Current is the mean value within 100ms.
- 3. The total IOL(peak) for ports P0, P1, P2, P8_6, P8_7, P9 and P10 must be 80mA max. The total IOL(peak) for ports P3, P4, P5, P6, P7 and P8_0 to P8_4 must be 80mA max. The total IOH(peak) for ports P0, P1, and P2 must be –40mA max. The total IOH(peak) for ports P6, P7, and P8_0 to P8_4 must be –40mA max. The total IOH(peak) for ports P6, P7, and P8_0 to P8_4 must be –40mA max.
 - The total IOH(peak) for ports P8_6, P8_7 and P9 must be -40mA max. Set Average Output Current to 1/2 of peak.
- 4. Relationship between main clock oscillation frequency, and supply voltage.

Main clock input oscillation frequency

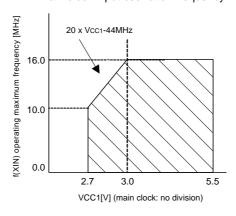


Table 5.3 A/D Conversion Characteristics (1)

Cumbal	Parame	to."		Managerina Condition		Standard	i	Unit
Symbol	Parame	ter	'	Measuring Condition	Min.	Тур.	Max.	Unit
_	Resolution		VREF=V	/cc		10		Bits
INL	Integral Non-Linearity Error	10bit	VREF= VCC= 5V	AN0 to AN7 input, AN0_0 to AN0_7 input, ANEX0, ANEX1 input			±5	LSB
			VREF= VCC= 3.3V	AN0 to AN7 input, AN0_0 to AN0_7 input, ANEX0, ANEX1 input			±7	LSB
		8bit	VREF=V	/cc=5V, 3.3V			±2	LSB
_	Absolute Accuracy	10bit	VREF= VCC= 5V	AN0 to AN7 input, AN0_0 to AN0_7 input, ANEX0, ANEX1 input			±5	LSB
			VREF= VCC =3.3V	AN0 to AN7 input, AN0_0 to AN0_7 input, ANEX0, ANEX1 input			±7	LSB
		8bit	VREF=V	/cc=5V, 3.3V			±2	LSB
-	Tolerance Level Impeda	ance				3		kΩ
DNL	Differential Non-Linearit	y Error					±2	LSB
-	Offset Error						±5	LSB
-	Gain Error						±5	LSB
RLADDER	Ladder Resistance		VREF=V	/cc	10		40	kΩ
tconv	10-bit Conversion Time Function Available	O-bit Conversion Time, Sample & Hold unction Available		/cc=5V, φAD=10MHz	3.3			μS
tconv	8-bit Conversion Time, Function Available	Sample & Hold	Hold VREF=Vcc=5V, \phiAD=10MHz		2.8			μS
tsamp	Sampling Time				0.3			μS
VREF	Reference Voltage				3.0		Vcc	V
VIA	Analog Input Voltage				0		VREF	V

- 1. Referenced to Vcc=AVcc=VREF=3.3 to 5.5V, Vss=AVss=0V at T_{opr} = -20 to $85^{\circ}C$ / -40 to $85^{\circ}C$ unless otherwise specified.
- 2. ϕAD frequency must be 10 MHz or less.
- 3. When sample & hold function is disabled, ϕAD frequency must be 250 kHz or more, in addition to the limitation in Note 2.
- 4. When sample & hold function is enabled, φAD frequency must be 1MHz or more, in addition to the limitation in Note 2.

Table 5.4 Flash Memory Version Electrical Characteristics (1)

Symbol	Parameter		Unit			
Symbol	Farameter	Min.	Тур.	Max.	Offic	
_	Program and Erase Endurance (2)		100 ⁽³⁾			cycle
_	Word Program Time (Vcc1=5.0V)			25	200	μS
_	Lock Bit Program Time		25	200	μS	
_	Block Erase Time	4-Kbyte block		0.3	4	S
_	(Vcc1=5.0V)	8-Kbyte block		0.3	4	S
_]	32-Kbyte block		0.5	4	S
_]	64-Kbyte block		0.8	4	s
tps	Flash Memory Circuit Stabilization Wait Time				15	μS
_	Data Hold Time (4)		10			year

- 1. Referenced to Vcc1=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (U3, U5) unless otherwise specified.
- 2. Program and Erase Endurance refers to the number of times a block erase can be performed. If the program and erase endurance is 100, each block can be erased 100 times. For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
- 3. Maximum number of E/W cycles for which operation is guaranteed.
- 4. Topr = -40 to 85 °C (U3) / -20 to 85 °C (U5).

Table 5.5 Flash Memory Version Program / Erase Voltage and Read Operation Voltage **Characteristics**

Flash Program, Erase Voltage	Flash Read Operation Voltage
$VCC1 = 3.3 \pm 0.3 \text{ V or } 5.0 \pm 0.5 \text{ (Topr} = 0^{\circ}\text{C to } 60^{\circ}\text{C)}$	VCC1=2.7 to 5.5 V (Topr = -40°C to 85°C (U3)
	-20°C to 85°C (U5))

Table 5.6 One Time Flash Version Electrical Characteristics (1)

Symbol	Parameter		Unit		
	i alametei		Тур.	Max.	Offic
_	Program Endurance			1	cycle
_	Word Program Time (Vcc1=5.0V)		50	500	μS
tPS	One Time Flash Memory Circuit Stabilization Wait Time			15	μS
_	Data Hold Time (4)	10			year

- 1. Referenced to Vcc1=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 $^{\circ}$ C (U3, U5) unless otherwise specified.
- 2. Topr = -40 to 85 $^{\circ}$ C (U3) / -20 to 85 $^{\circ}$ C (U5).

Table 5.7 One Time Flash Version Program Voltage and Read Operation Voltage Characteristics

Flash Program Voltage	Flash Read Operation Voltage
$VCC1 = 3.3 \pm 0.3 \text{ V or } 5.0 \pm 0.5 \text{ (Topr} = 0^{\circ}\text{C to } 60^{\circ}\text{C} \text{)}$	VCC1= 2.7 to 5.5 V (Topr = -40° C to 85° C (U3)
	-20°C to 85°C (U5))

Table 5.8 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition		Unit		
	Farameter	Measuring Condition	Min.	Тур.	Max.	Offic
td(P-R)	Time for Internal Power Supply Stabilization During Powering-On	Vcc=2.7V to 5.5V			2	ms
td(R-S)	STOP Release Time				1500	μS
td(W-S)	Low Power Dissipation Mode Wait Mode Release Time				1500	μS

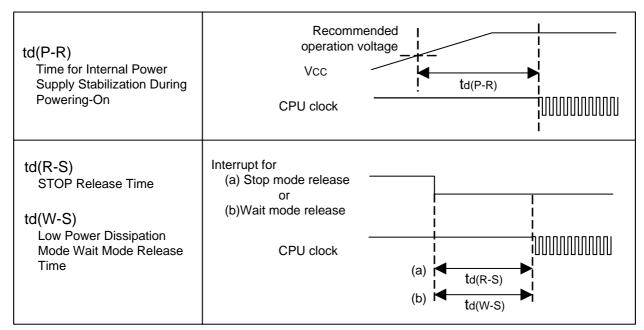


Figure 5.1 Power Supply Circuit Timing Diagram

VCC1=VCC2=5V

Electrical Characteristics(1) (1) Table 5.9

Symbol		Param	otor	Measuring Condition	Sta	andard		Unit
Symbol		Faiaiii	etei	ivieasuring Condition	Min.	Тур.	Max.	Offic
Vон	HIGH Output Voltage	put P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7,		IOH=-5mA	Vcc-2.0		Vcc	V
Vон	HIGH Output Voltage	Output P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7,		ΙΟΗ=-200μΑ	Vcc-0.3		Vcc	V
Vон	HIGH Outpu	t Voltage XOUT	HIGHPOWER	IOH=-1mA	Vcc-2.0		Vcc	V
			LOWPOWER	IOH=-0.5mA	Vcc-2.0		Vcc	V
	HIGH Outpu	t Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
			LOWPOWER	With no load applied		1.6		V
VoL	LOW Output Voltage	P3_0 to P3_7, P4_0 P6_0 to P6_7, P7_0	to P1_7, P2_0 to P2_7, to P4_7, P5_0 to P5_7, to P7_7, P8_0 to P8_4, to P9_7, P10_0 to P10_7	IOL=5mA			2.0	٧
Vol	LOW Output Voltage	P3_0 to P3_7, P4_0 P6_0 to P6_7, P7_0	to P1_7, P2_0 to P2_7, to P4_7, P5_0 to P5_7, to P7_7, P8_0 to P8_4, to P9_7, P10_0 to P10_7	IOL=200μA			0.45	V
Vol	LOW Output	Voltage XOUT	HIGHPOWER	IOL=1mA			2.0	V
			LOWPOWER	IOL=0.5mA			2.0	V
	LOW Output	Voltage XCOUT	HIGHPOWER	With no load applied		0		V
			LOWPOWER	With no load applied		0		V
VT+-VT-	Hysteresis	CLK0 to CLK2, TA0	OIN to TB2IN, ADTRG, CTS0 to CTS2, OUT to TA2OUT, KI0 to KI3, L0 to SCL2, SDA0 to SDA2		0.2		1.0	V
VT+-VT-	Hysteresis	RESET			0.2		2.5	V
lін	HIGH Input Current	P3_0 to P3_7, P4_0	_ :	VI=5V			5.0	μА
lıL	LOW Input Current	OW Input P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7,		VI=0V			-5.0	μА
RPULLUP	Pull-Up Resistance	ull-Up P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7,		Vi=0V	30	50	170	kΩ
RfXIN	Feedback R	esistance XIN				1.5		МΩ
RfXCIN	Feedback R	esistance XCIN				15		МΩ
VRAM	RAM Retent	ion Voltage		At stop mode	2.0			V

NOTES: 1. Referenced to Vcc1=Vcc2=4.2 to 5.5V, Vss = 0V at T_{opr} = -20 to 85° C / -40 to 85° C, f(XIN) =16MHz unless otherwise specified.

Electrical Characteristics (2) (1) **Table 5.10**

Cymphal	Doromot	0.5	Maga	uring Condition	;	Standard	t	Unit
Symbol	Paramet	eı	ivieas	uring Condition	Min. Typ. Max.		Max.	Unit
Icc	Power Supply Current (Vcc1=Vcc2=4.0V to 5.5V)	In single-chip mode, the output	Mask ROM	f(XIN)=16MHz No division		10	15	mA
	,	pins are open and other pins are Vss	One Time Flash	f(XIN)=16MHz, No division		10	18	mA
			Flash Memory	f(XIN)=16MHz, No division		12	18	mA
			One Time Flash	f(XIN)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Program	f(XIN)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Erase	f(XIN)=10MHz, VCC1=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM ⁽³⁾		25		μА
			One Time Flash	f(XCIN)=32kHz Low power dissipation mode, RAM ⁽³⁾		25		μА
				f(XCIN)=32kHz Low power dissipation mode, Flash Memory ⁽³⁾		350		μА
			Flash Memory	f(XCIN)=32kHz Low power dissipation mode, RAM ⁽³⁾		25		μА
				f(XCIN)=32kHz Low power dissipation mode, Flash Memory ⁽³⁾		420		μА
			Mask ROM One Time Flash Flash Memory	f(XCIN)=32kHz Wait mode ⁽²⁾ , Oscillation capability High		7.5		μА
		i idəli ivicilidiy	f(XCIN)=32kHz Wait mode ⁽²⁾ , Oscillation capability Low		2.0		μА	
				Stop mode Topr =25°C		0.8	3.0	μА

NOTES:

1. Referenced to Vcc1=Vcc2=4.2 to 5.5V, Vss = 0V at Topr = -20 to 85°C / -40 to 85°C, f(XIN)=16MHz unless otherwise specified.

2. With one timer operated using fC32.

3. This indicates the memory in which the program to be executed exists.

VCC1=VCC2=5V

Timing Requirements

(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = -20 to 85°C / -40 to 85°C unless otherwise specified)

Table 5.11 External Clock Input (XIN input) (1)

Symbol	Parameter	Stan	dard	Unit
	Farameter	Min.	Max.	Offic
t c	External Clock Input Cycle Time	62.5		ns
tw(H)	External Clock Input HIGH Pulse Width	25		ns
tw(L)	External Clock Input LOW Pulse Width	25		ns
tr	External Clock Rise Time		15	ns
tf	External Clock Fall Time		15	ns

NOTES:

1. The condition is Vcc1=Vcc2=3.0 to 5.0V.

Table 5.12 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Stan	dard	Unit
Symbol	Farameter	Min.	Max.	Offit
tac1(RD-DB)	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
tac2(RD-DB)	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
tsu(DB-RD)	Data Input Setup Time	40		ns
tsu(RDY-BCLK)	RDY Input Setup Time	30		ns
tsu(HOLD-BCLK)	HOLD Input Setup Time	40		ns
th(RD-DB)	Data Input Hold Time	0		ns
th(BCLK-RDY)	RDY Input Hold Time	0		ns
th(BCLK-HOLD)	HOLD Input Hold Time	0		ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 45[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)x10^9}{f(BCLK)} - 45[ns] \qquad \text{n is "2" for 1-wait setting.}$$

VCC1=VCC2=5V

Timing Requirements

(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.13 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
	Farameter	Min.	Max.	
tc(TA)	TAilN Input Cycle Time	100		ns
tw(TAH)	TAilN Input HIGH Pulse Width	40		ns
tw(TAL)	TAilN Input LOW Pulse Width	40		ns

Table 5.14 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Stan	dard	Linit
	Farantelei	Min.	Max.	Unit ns
tc(TA)	TAilN Input Cycle Time	400		ns
tw(TAH)	TAilN Input HIGH Pulse Width	200		ns
tw(TAL)	TAilN Input LOW Pulse Width	200		ns

Table 5.15 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Stan	dard	Linit
	Faranteter	Min.	Max.	Unit ns
tc(TA)	TAilN Input Cycle Time	200		ns
tw(TAH)	TAilN Input HIGH Pulse Width	100		ns
tw(TAL)	TAilN Input LOW Pulse Width	100		ns

Table 5.16 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Cumbal	Parameter	Stan	Max.	Unit
Symbol	Farameter	Min.	Max.	Offit
tw(TAH)	TAIIN Input HIGH Pulse Width	100		ns
tw(TAL)	TAilN Input LOW Pulse Width	100		ns

Table 5.17 Timer A Input (Counter Increment/Decrement Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
	Faranteter	Min.	Max.	Offit
tc(UP)	TAiOUT Input Cycle Time	2000		ns
tw(UPH)	TAiOUT Input HIGH Pulse Width	1000		ns
tw(UPL)	TAiOUT Input LOW Pulse Width	1000		ns
tsu(UP-TIN)	TAiOUT Input Setup Time	400		ns
th(TIN-UP)	TAiOUT Input Hold Time	400		ns

Table 5.18 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Stan	Standard Min. Max.	Unit
	Falanielei	Min.	Max.	Unit ns
tc(TA)	TAilN Input Cycle Time	800		ns
tsu(TAIN-TAOUT)	TAiOUT Input Setup Time	200		ns
tsu(TAOUT-TAIN)	TAilN Input Setup Time	200		ns

VCC1=VCC2=5V

Timing Requirements

(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = -20 to 85°C / -40 to 85°C unless otherwise specified)

Table 5.19 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Stan	dard	Unit
	Faranielei	Min.	Max.	Offit
tc(TB)	TBilN Input Cycle Time (counted on one edge)	100		ns
tw(TBH)	TBilN Input HIGH Pulse Width (counted on one edge)	40		ns
tw(TBL)	TBilN Input LOW Pulse Width (counted on one edge)	40		ns
tc(TB)	TBilN Input Cycle Time (counted on both edges)	200		ns
tw(TBH)	TBilN Input HIGH Pulse Width (counted on both edges)	80		ns
tw(TBL)	TBilN Input LOW Pulse Width (counted on both edges)	80		ns

Table 5.20 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Stan	dard	Unit
	Farameter	Min.	Max.	
tc(TB)	TBilN Input Cycle Time	400		ns
tw(TBH)	TBilN Input HIGH Pulse Width	200		ns
tw(TBL)	TBilN Input LOW Pulse Width	200		ns

Table 5.21 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Stan	dard	Unit
	Farameter	Min.	Max.	Unit ns
tc(TB)	TBilN Input Cycle Time	400		ns
tw(TBH)	TBilN Input HIGH Pulse Width	200		ns
tw(TBL)	TBilN Input LOW Pulse Width	200		ns

Table 5.22 A/D Trigger Input

Symbol	Parameter	Stan	Max.	Unit
	Falametei	Min.		Offic
tc(AD)	ADTRG Input Cycle Time	1000		ns
tw(ADL)	ADTRG input LOW Pulse Width	125		ns

Serial Interface Table 5.23

Symbol	Parameter	Standard		Unit
		Min.	Max.	Offit
tc(CK)	CLKi Input Cycle Time	200		ns
tw(CKH)	CLKi Input HIGH Pulse Width	100		ns
tw(CKL)	CLKi Input LOW Pulse Width	100		ns
td(C-Q)	TXDi Output Delay Time		80	ns
th(C-Q)	TXDi Hold Time	0		ns
tsu(D-C)	RXDi Input Setup Time	70		ns
th(C-D)	RXDi Input Hold Time	90		ns

Table 5.24 External Interrupt INTi Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	Offic
tw(INH)	INTi Input HIGH Pulse Width	250		ns
tw(INL)	INTi Input LOW Pulse Width	250		ns

VCC1=VCC2=5V

Switching Characteristics

(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.25 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Stan	dard	Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time			25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		-3		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)	See Figure 5.2	(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		-3		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		-4		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 40[ns] \qquad \qquad f(BCLK) \text{ is } 12.5 \text{MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.

Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.

Hold time of data bus is expressed in

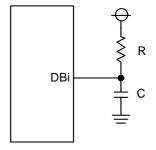
$$t = -CR \times In (1-VoL / Vcc1)$$

by a circuit of the right figure.

For example, when Vol = 0.2Vcc1, C = 30pF, R = 1k Ω , hold time of output "L" level is

$$t = -30pF X 1k \Omega X In(1-0.2Vcc1 / Vcc1)$$

= 6.7 ns.



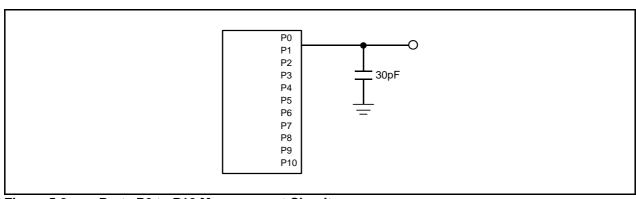


Figure 5.2 Ports P0 to P10 Measurement Circuit

VCC1=VCC2=5V

Switching Characteristics

(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.26 Memory Expansion and Microprocessor Modes (for 1 wait setting and external area access)

Symbol	Parameter		Stan	dard	Unit
Syllibol	Farameter		Min.	Max.	Offic
td(BCLK-AD)	Address Output Delay Time			25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		-3		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		-3		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time	0	-4		ns
td(BCLK-RD)	RD Signal Output Delay Time	See Figure 5.2		25	ns
th(BCLK-RD)	RD Signal Output Hold Time	I iguie 3.2	0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR)(3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)x10^9}{f(BCLK)} - 40[ns] \qquad \text{n is "1" for 1-wait setting, f(BCLK) is 12.5MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.

Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.

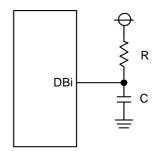
Hold time of data bus is expressed in

t = -CR X In (1-VoL / Vcc1)

by a circuit of the right figure.

For example, when Vol = 0.2Vcc1, C = 30pF, R = 1k Ω , hold time of output "L" level is

t = -30pF X 1k Ω X In(1-0.2Vcc1 / Vcc1) = 6.7ns.



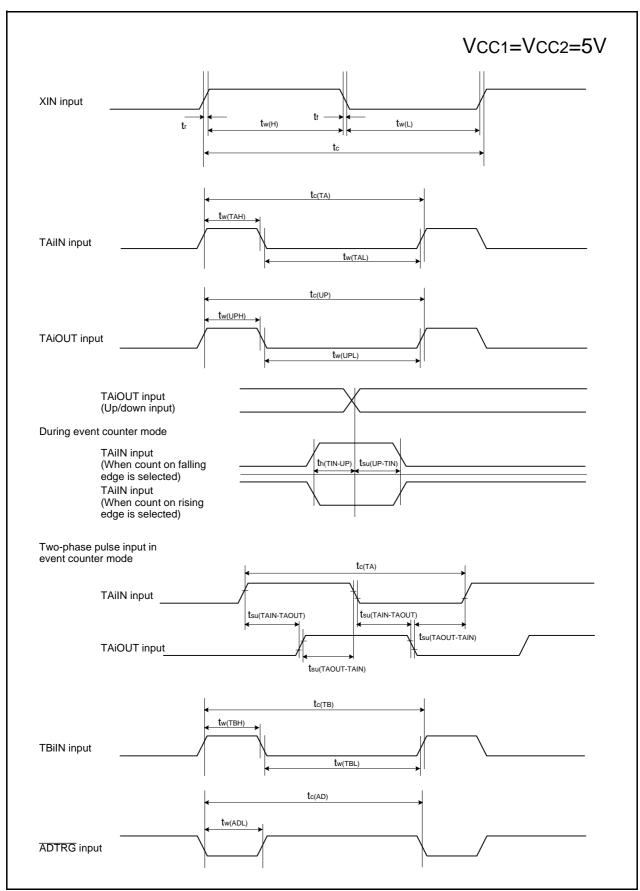
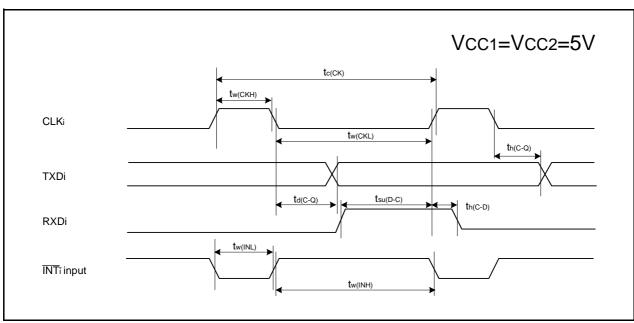


Figure 5.3 Timing Diagram (1)



Timing Diagram (2) Figure 5.4

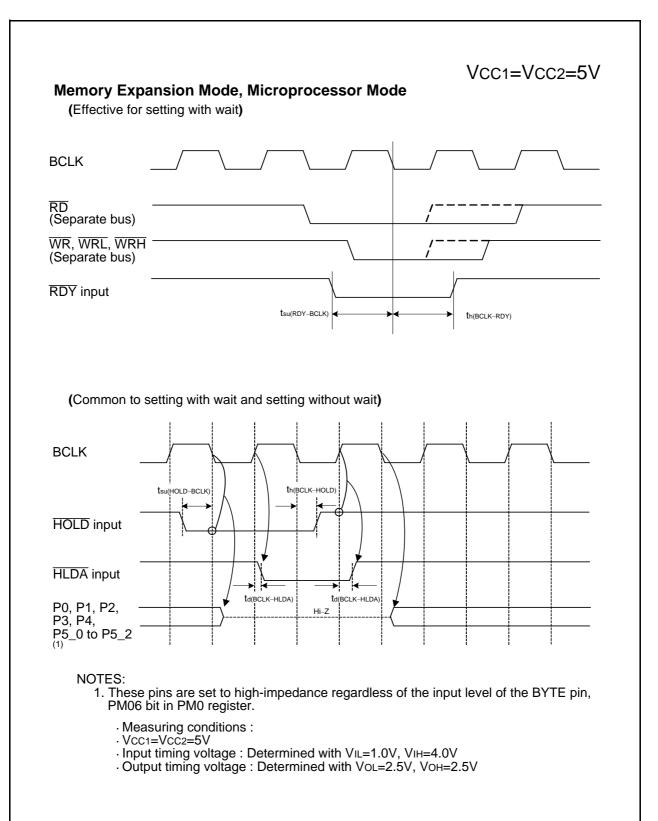


Figure 5.5 Timing Diagram (3)

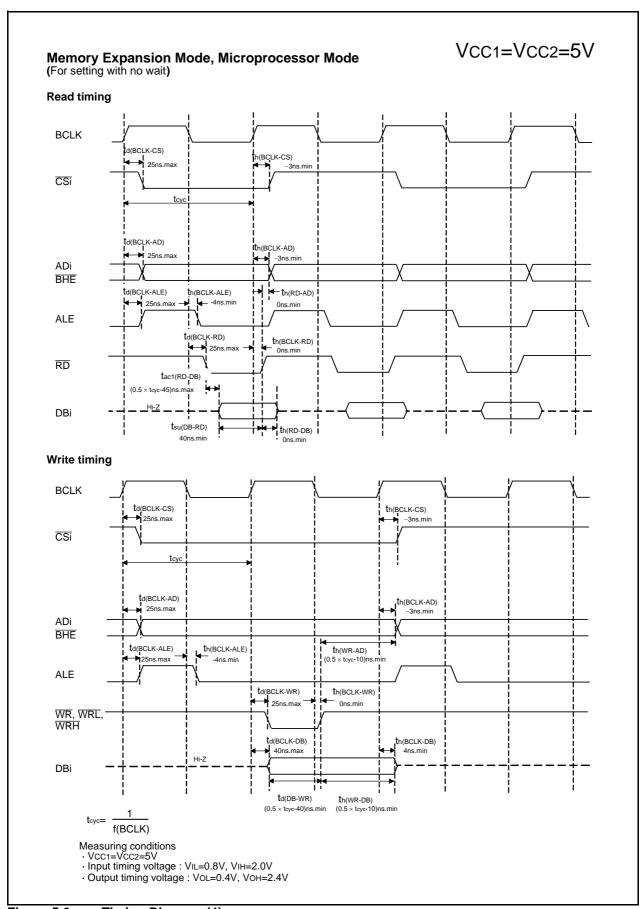


Figure 5.6 Timing Diagram (4)

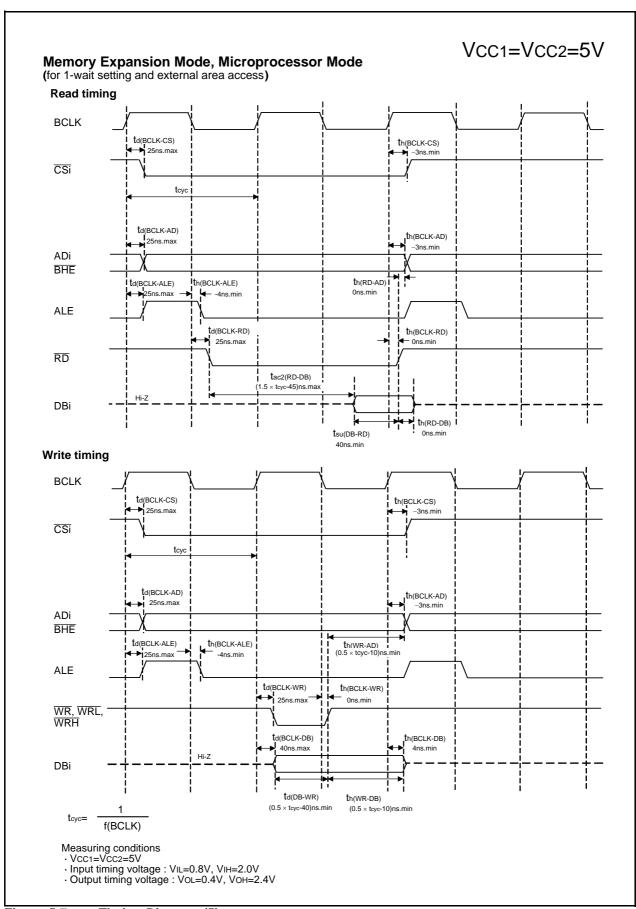


Figure 5.7 Timing Diagram (5)

VCC1=VCC2=3V

Electrical Characteristics (1) (1) **Table 5.27**

C. mak al	Parameter		Manageria a Canaditia a	St	andard		Unit	
Symbol		Parameter		Measuring Condition	Min.	Тур.	Max.	Unit
Vон	HIGH Output Voltage	P3_0 to P3_7, P4_0 to P6_0 to P6_7, P7_2 to	o P1_7, P2_0 to P2_7, o P4_7, P5_0 to P5_7, o P7_7, P8_0 to P8_4, P9_7, P10_0 to P10_7	IOH=-1mA	Vcc-0.5		Vcc	V
Vон	HIGH Outpu	t Voltage XOUT	HIGHPOWER	IOH=-0.1mA	Vcc-0.5		Vcc	V
			LOWPOWER	Іон=-50μΑ	Vcc-0.5		Vcc	V
	HIGH Outpu	t Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
			LOWPOWER	With no load applied		1.6		V
VoL	LOW Output Voltage	P3_0 to P3_7, P4_0 to P6_0 to P6_7, P7_0 to	o P1_7, P2_0 to P2_7, o P4_7, P5_0 to P5_7, o P7_7, P8_0 to P8_4, P9_7, P10_0 to P10_7	IoL=1mA			0.5	V
Vol	LOW Output	Voltage XOUT	HIGHPOWER	IoL=0.1mA			0.5	V
			LOWPOWER	IoL=50μA			0.5	V
	LOW Output	Voltage XCOUT	HIGHPOWER	With no load applied		0		V
			LOWPOWER	With no load applied		0		V
VT+-VT-	Hysteresis	TAOIN to TA2IN, TBOIN to TB2IN, INTO ADTRG, CTS0 to CTS CLK0 to CLK2, TA00 KIO to KI3, SCL0 to S	S2, RXD0 to RXD2, UT to TA2OUT,		0.2		0.8	V
VT+-VT-	Hysteresis	RESET			0.2	(0.7)	1.8	V
lін	HIGH Input Current		P7_7, P8_0 to P8_7, to P10_7,	VI=3V			4.0	μА
lıL	LOW Input Current	P0_0 to P0_7, P1_0 to P3_0 to P3_7, P4_0 to P6_0 to P6_7, P7_0 to P9_0 to P9_7, P10_0 XIN, RESET, CNVSS	P7_7, P8_0 to P8_7, to P10_7,	VI=0V			-4.0	μА
RPULLUP	Pull-Up Resistance	P3_0 to P3_7, P4_0 to P6_0 to P6_7, P7_2 to	D P1_7, P2_0 to P2_7, D P4_7, P5_0 to P5_7, D P7_7, P8_0 to P8_4, P9_7, P10_0 to P10_7	Vi=0V	50	100	500	kΩ
RfXIN	Feedback R	esistance	XIN			3.0		МΩ
RfXCIN	Feedback R	esistance	XCIN			25		МΩ
VRAM	RAM Retent	ion Voltage		At stop mode	2.0			V

NOTES:

^{1.} Referenced to Vcc1 = Vcc2 = 2.7 to 3.3V, Vss = 0V at Topr = -20 to $85^{\circ}C$ / -40 to $85^{\circ}C$, f(XIN)=10MHz no wait unless otherwise specified.

Table 5.28 Electrical Characteristics (2) (1)

Symbol	Doromot	Parameter Measuring Condition		,	Standar	b	Unit	
Symbol	Faramen	eı	Measuring Condition		Min.	Тур.	Max.	Offic
Icc	Power Supply Current (Vcc1=Vcc2=2.7V to 3.6V)	In single-chip mode, the output	Mask ROM	f(XIN)=10MHz No division		8	11	mA
		pins are open and other pins are Vss	One Time Flash	f(XIN)=10MHz, No division		8	13	mA
			Flash Memory	f(XIN)=10MHz, No division		8	13	mA
			Flash Memory Program	f(XIN)=10MHz, VCC1=3.0V		12		mA
,			One Time Flash Program	f(XIN)=10MHz, VCC1=3.0V		12		mA
			Flash Memory Erase	f(XIN)=10MHz, VCC1=3.0V		22		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM ⁽³⁾		25		μА
,			One Time Flash	f(XCIN)=32kHz Low power dissipation mode, RAM ⁽³⁾		25		μА
				f(XCIN)=32kHz Low power dissipation mode, Flash Memory ⁽³⁾		350		μА
			Flash Memory	f(XCIN)=32kHz Low power dissipation mode, RAM ⁽³⁾		25		μА
				f(XCIN)=32kHz Low power dissipation mode, Flash Memory (3)		420		μА
			Mask ROM One Time Flash Flash Memory	f(XCIN)=32kHz Wait mode ⁽²⁾ , Oscillation capability High		6.0		μА
				f(XCIN)=32kHz Wait mode ⁽²⁾ , Oscillation capability Low		1.8		μА
				Stop mode Topr =25°C		0.7	3.0	μА

NOTES:

^{1.} Referenced to Vcc1=Vcc2=2.7 to 3.3V, Vss = 0V at Topr = -20 to 85°C / -40 to 85°C, f(XIN)=10MHz unless otherwise

<sup>specified.
With one timer operated using fC32.
This indicates the memory in which the program to be executed exists.</sup>

VCC1=VCC2=3V

Timing Requirements

(VCC1 = VCC2 = 3V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.29 External Clock Input (XIN input)

Symbol	mbol Parameter -	Stan	Unit	
Symbol		Min.	Max.	Offic
tc	External Clock Input Cycle Time	(NOTE 2)		ns
tw(H)	External Clock Input HIGH Pulse Width	(NOTE 3)		ns
tw(L)	External Clock Input LOW Pulse Width	(NOTE 3)		ns
tr	External Clock Rise Time		(NOTE 4)	ns
tf	External Clock Fall Time		(NOTE 4)	ns

NOTES:

- 1. The condition is Vcc1=Vcc2=2.7 to 3.0V.
- 2. Calculated according to the Vcc1 voltage as follows:

$$\frac{10^{-6}}{20 \times V \text{CC1} - 44} \text{ [ns]}$$

3. Calculated according to the Vcc1 voltage as follows:

$$\frac{10^{-6}}{20 \times V\text{CC1} - 44} \times 0.4 \text{ [ns]}$$

4. Calculated according to the Vcc1 voltage as follows:

$$-10 \times Vcc1 + 45 [ns]$$

Table 5.30 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Stan	Unit	
Symbol	Faranielei	Min.	Max.	Offit
tac1(RD-DB)	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
tac2(RD-DB)	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
tsu(DB-RD)	Data Input Setup Time	50		ns
tsu(RDY-BCLK)	RDY Input Setup Time	40		ns
tsu(HOLD-BCLK)	HOLD Input Setup Time	50		ns
th(RD-DB)	Data Input Hold Time	0		ns
th(BCLK-RDY)	RDY Input Hold Time	0		ns
th(BCLK-HOLD)	HOLD Input Hold Time	0		ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5x10^9}{f(BCLK)} - 60[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)x10^9}{f(BCLK)} - 60[ns] \qquad \text{n is "2" for 1-wait setting.}$$



Vcc1=Vcc2=3V

Timing Requirements

(VCC1 = VCC2 = 3V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.31 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Symbol Parameter	Stan	Unit	
Symbol		Min.	Max.	Offit
tc(TA)	TAilN Input Cycle Time	150		ns
tw(TAH)	TAilN Input HIGH Pulse Width	60		ns
tw(TAL)	TAilN Input LOW Pulse Width	60		ns

Table 5.32 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Stan	Unit	
	Farameter	Min.	Max.	Offit
tc(TA)	TAilN Input Cycle Time	600		ns
tw(TAH)	TAilN Input HIGH Pulse Width	300		ns
tw(TAL)	TAilN Input LOW Pulse Width	300		ns

Table 5.33 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Stan	Unit	
	Farameter	Min.	Max.	Offic
tc(TA)	TAilN Input Cycle Time	300		ns
tw(TAH)	TAilN Input HIGH Pulse Width	150		ns
tw(TAL)	TAilN Input LOW Pulse Width	150		ns

Table 5.34 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Cumbal	Symbol Parameter -	Stan	Unit	
Symbol		Min.	Max.	Offit
tw(TAH)	TAilN Input HIGH Pulse Width	150		ns
tw(TAL)	TAilN Input LOW Pulse Width	150		ns

Table 5.35 Timer A Input (Counter Increment/Decrement Input in Event Counter Mode)

Symbol	Parameter -	Stan	Unit	
Symbol		Min.	Max.	Offit
tc(UP)	TAiOUT Input Cycle Time	3000		ns
tw(UPH)	TAiOUT Input HIGH Pulse Width	1500		ns
tw(UPL)	TAiOUT Input LOW Pulse Width	1500		ns
tsu(UP-TIN)	TAiOUT Input Setup Time	600		ns
th(TIN-UP)	TAiOUT Input Hold Time	600		ns

Table 5.36 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Stan	Unit	
	Falanielei	Min.	Max.	Offit
tc(TA)	TAilN Input Cycle Time	2		μS
tsu(TAIN-TAOUT)	TAiOUT Input Setup Time	500		ns
tsu(TAOUT-TAIN)	TAilN Input Setup Time	500		ns

VCC1=VCC2=3V

Timing Requirements

(VCC1 = VCC2 = 3V, Vss = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Stan	Unit	
Symbol	Faranielei	Min.	Max.	Offic
tc(TB)	TBilN Input Cycle Time (counted on one edge)	150		ns
tw(TBH)	TBilN Input HIGH Pulse Width (counted on one edge)	60		ns
tw(TBL)	TBilN Input LOW Pulse Width (counted on one edge)	60		ns
tc(TB)	TBilN Input Cycle Time (counted on both edges)	300		ns
tw(TBH)	TBilN Input HIGH Pulse Width (counted on both edges)	120		ns
tw(TBL)	TBilN Input LOW Pulse Width (counted on both edges)	120		ns

Table 5.38 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit	
Symbol	Falametei	Min.	Max.	Offic	
tc(TB)	TBilN Input Cycle Time	600		ns	
tw(TBH)	TBilN Input HIGH Pulse Width	300		ns	
tw(TBL)	TBilN Input LOW Pulse Width		ns		

Table 5.39 Timer B Input (Pulse Width Measurement Mode)

Cymbol	Parameter	Stan	dard	Unit
Symbol	Farameter	Min.	Max.	Offit
tc(TB)	TBilN Input Cycle Time	600		ns
tw(TBH)	TBilN Input HIGH Pulse Width	300		ns
tw(TBL)	TBilN Input LOW Pulse Width	300		ns

Table 5.40 A/D Trigger Input

Symbol	Parameter	Stan	Unit	
Symbol	Farameter	Min.	Max.	Offit
tc(AD)	ADTRG Input Cycle Time	1500		ns
tw(ADL)	ADTRG Input LOW Pulse Width	200		ns

Table 5.41 Serial Interface

Symbol	Parameter	Stan	Unit	
Symbol	Falametei	Min.	Max.	Offic
tc(CK)	CLKi Input Cycle Time	300		ns
tw(CKH)	CLKi Input HIGH Pulse Width	150		ns
tw(CKL)	CLKi Input LOW Pulse Width	150		ns
td(C-Q)	TXDi Output Delay Time		160	ns
th(C-Q)	TXDi Hold Time	0		ns
tsu(D-C)	RXDi Input Setup Time	100		ns
th(C-D)	RXDi Input Hold Time	90		ns

External Interrupt INTi Input **Table 5.42**

Cumbal	Parameter	Stan	Unit	
Symbol	Farameter	Min.	Max.	Offit
tw(INH)	INTi Input HIGH Pulse Width	380		ns
tw(INL)	INTi Input LOW Pulse Width	380		ns

VCC1=VCC2=3V

Switching Characteristics

(VCC1 = VCC2 = 3V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.43 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit	
Symbol	Falametei		Min.	Max.	Offic	
td(BCLK-AD)	Address Output Delay Time			30	ns	
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		0		ns	
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns	
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns	
td(BCLK-CS)	Chip Select Output Delay Time			30	ns	
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		0		ns	
td(BCLK-ALE)	ALE Signal Output Delay Time		25	ns		
th(BCLK-ALE)	ALE Signal Output Hold Time	-4		ns		
td(BCLK-RD)	RD Signal Output Delay Time	See Figure 5.8		30	ns	
th(BCLK-RD)	RD Signal Output Hold Time	rigure 3.0	0		ns	
td(BCLK-WR)	WR Signal Output Delay Time			30	ns	
th(BCLK-WR)	WR Signal Output Hold Time		0		ns	
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns	
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		ns			
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns	
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)	1	(NOTE 2)		ns	
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns	

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 40[ns]$$
 f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.

Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.

Hold time of data bus is expressed in

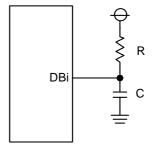
$$t = -CR \times In (1-VoL / Vcc1)$$

by a circuit of the right figure.

For example, when Vol = 0.2Vcc1, C = 30pF, R = 1k Ω , hold time of output "L" level is

$$t = -30pF X 1k \Omega X In(1-0.2Vcc1 / Vcc1)$$

= 6.7 ns.



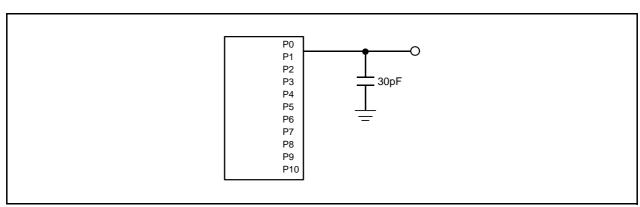


Figure 5.8 Ports P0 to P10 Measurement Circuit

VCC1=VCC2=3V

Switching Characteristics

(VCC1 = VCC2 = 3V, VSS = 0V, at Topr = -20 to 85° C / -40 to 85° C unless otherwise specified)

Table 5.44 Memory Expansion and Microprocessor Modes (for 1 wait setting and external area access)

Cumbal	Doromotor		Stan	Standard		
Symbol	Parameter		Min.	Max.	Unit	
td(BCLK-AD)	Address Output Delay Time			30	ns	
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		0		ns	
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns	
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns	
td(BCLK-CS)	Chip Select Output Delay Time			30	ns	
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		0		ns	
td(BCLK-ALE)	ALE Signal Output Delay Time			25	ns	
th(BCLK-ALE)	ALE Signal Output Hold Time	0	-4		ns	
td(BCLK-RD)	RD Signal Output Delay Time	See Figure 5.8		30	ns	
th(BCLK-RD)	RD Signal Output Hold Time	r igure 5.5	0		ns	
td(BCLK-WR)	WR Signal Output Delay Time			30	ns	
th(BCLK-WR)	WR Signal Output Hold Time		0		ns	
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns	
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns	
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns	
th(WR-DB)	Data Output Hold Time (in relation to WR)(3)		(NOTE 2)		ns	
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns	

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)x10^9}{f(BCLK)} - 40[ns] \qquad \text{n is "1" for 1-wait setting, } f(BCLK) \text{ is 12.5MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5x10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.

Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.

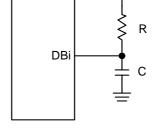
Hold time of data bus is expressed in

t = -CR X In (1-VoL / Vcc1)

by a circuit of the right figure.

For example, when Vol = 0.2Vcc1, C = 30pF, R = 1k Ω , hold time of output "L" level is

 $t = -30pF X 1k\Omega X In(1-0.2Vcc1 / Vcc1)$ = 6.7ns.



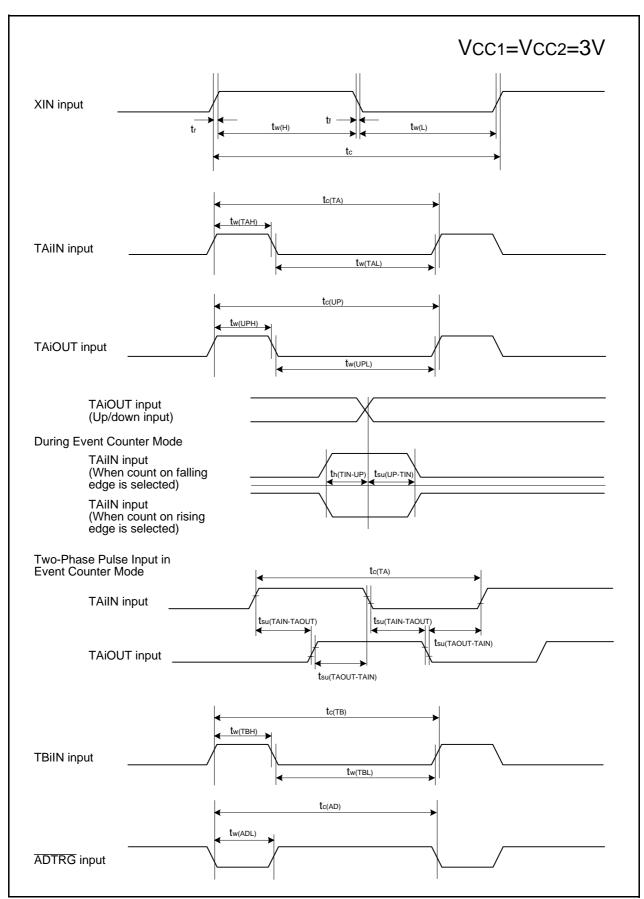


Figure 5.9 Timing Diagram (1)

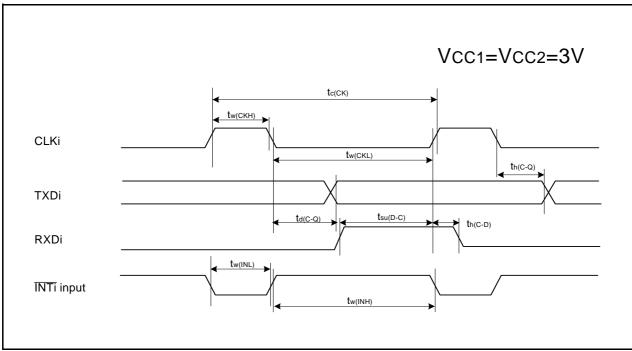


Figure 5.10 Timing Diagram (2)

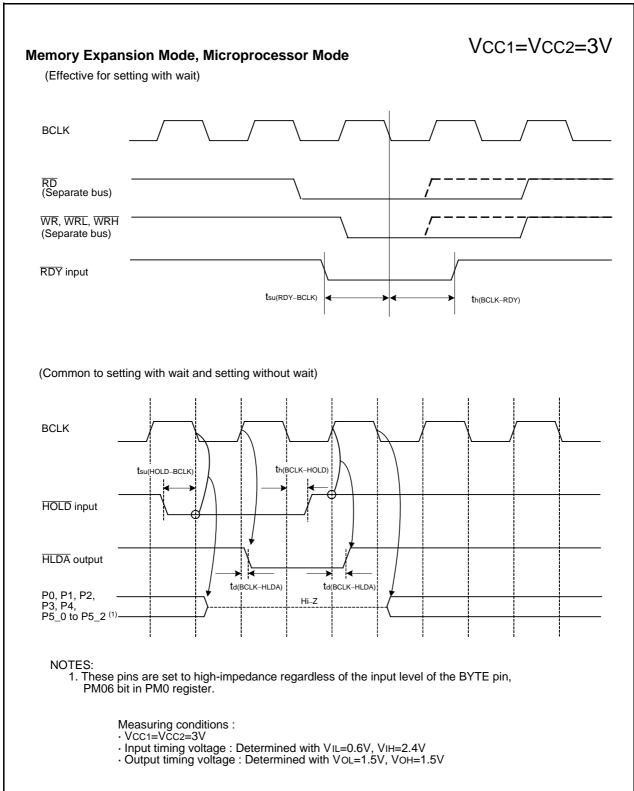


Figure 5.11 Timing Diagram (3)

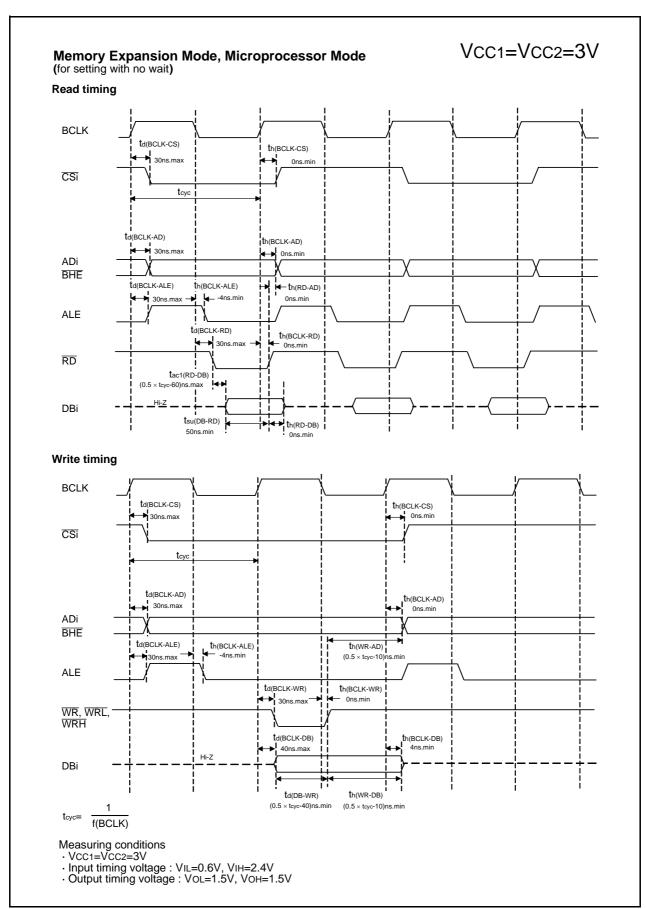
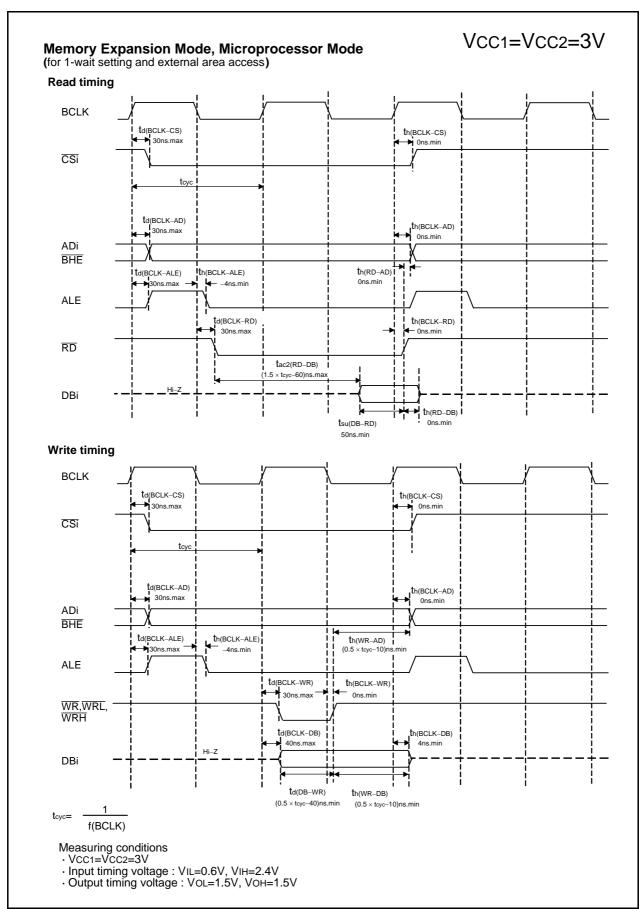


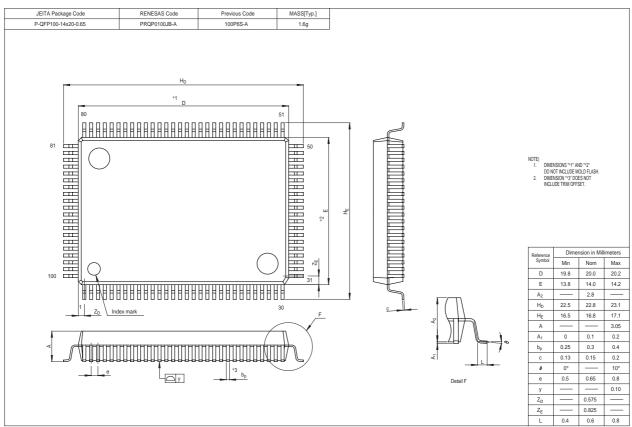
Figure 5.12 Timing Diagram (4)

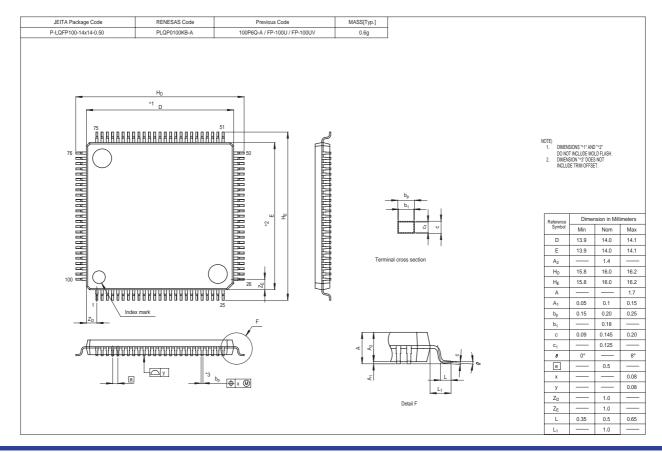


Timing Diagram (5) Figure 5.13

Appendix 1. Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the "Packages" section of the Renesas Technology website.





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M16C/30P Group Datasheet

D	Dete		Description
Rev.	Date	Page	Summary
0.70	Aug 26, 2004	_	First Edition issued
0.80	Mar 18, 2005	_	development support tools -> development tools
		_	BCLK -> CPU clock
		2	Table 1.1 Performance Outline of M16C/30P Group Serial interface is revised.
		4	Figure 1.2 Type., Memory Size, and Package is partly revised.
		8	Table 1.4 Pin Detection (2) is partly revised.
		20	Note 2 Table 5.3 A/D Conversion Characteristics is partly revised.
		21	Symbol of Table 5.4 Power Supply Circuit Timing Characteristics is partly revised.
		22	Table 5.5 Electrical Characteristics is revised.
		28	Table 5.19 Electrical Characteristics is revised.
1.00	Sep 01, 2005	2	Table 1.1 Performance Outline of M16C/30P Group is partly revised.
		4	Table 1.2 Product List is partly revised.
			Figure 1.2 Type No., Memory Size, and Package is partly revised.
		5	Figure 1.3 Pin Configuration is partly revised.
		6	Figure 1.4 Pin Configuration is partly revised.
		7-8	Tables 1.3 to 1.4 Pin Characteristics are added.
		9	Table 1.5 Pin Description is revised.
		14	3. Memory is partly revised.
		15	Table 4.1 SFR Information is partly revised.
		19	Table 4.5 SFR Information is partly revised
		21	Table 5.2 Recommended Operating Conditions is partly revised.
		22	Table 5.3 A/D Conversion Characteristics is partly revised.
		25	Note 1 is added in Table 5.6 External Clock Input (XIN input)
			Table 5.7 Memory Expansion Mode and Microprocessor Mode is added.
		28	Table 5.20 Memory Expansion Mode and Microprocessor Modes (for setting with no wait) is added.
			Figure 5.2 Ports P0 to P10 Measurement Circuit is added.
		29	Table 5.21 Memory Expansion Mode and Microprocessor Modes (for 1- to 3-wait setting and external area access) is added.
		32	Figure 5.5 Timing Diagram (3) is added.
		33	Figure 5.6 Timing Diagram (4) is added.
		34	Figure 5.7 Timing Diagram (5) is added.
		36	Note 1 to 4 are added in Table 5.23 External Clock Input (XIN input)
			Table 5.24 Memory Expansion Mode and Microprocessor Mode is added.
		39	Table 5.37 Memory Expansion Mode and Microprocessor Modes (for setting with no wait) is added.
			Figure 5.8 Ports P0 to P10 Measurement Circuit is added.
		40	Table 5.38 Memory Expansion Mode and Microprocessor Modes (for 1- to 3-wait setting and external area access) is added.
		43	Figure 5.11 Timing Diagram (3) is added.

REVISION HISTORY

M16C/30P Group Datasheet

Rev.	Doto	Description	
Rev.	Date	Page	Summary
		44	Figure 5.12 Timing Diagram (4) is added.
		45	Figure 5.13 Timing Diagram (5) is added.
1.10	Oct 01, 2005	2	Table 1.1 Performance Outline of M16C/30P Group is partly revised.
		4	Table 1.2 Product List is partly revised.
			Figure 1.2 Type No., Memory Size, and Package is partly revised.
		5	Table 1.3 Product Code of Mask ROM version Version for M16C/30P is added.
			Figure 1.3 Marking Diagram of Mask ROM Version for M16C/30P is added.
		6	Figure 1.4 Marking Diagram of ROM -less Version for M16C/30P is added.
		6	Table 1.4 Product Code of ROM-less version for M16C/30P is added.
		16	Figure 3.1 Memory Map is partly added.
		23	Table 5.2 information is revised.
1.11	May 31, 2006	4	1.4 Product List information is revised.
			Table 1.2 Product List is partly revised.
		5	Figure 1.2 Type No., Memory Size, and Package is partly added.
		7	Table 1.4 Product Code of Flash Memory version and ROM-less version for M16C/30P is partly revised.
			Figure 1.4 Marking Diagram of Flash Memory version and ROM-less Version for M16C/30P (Top View) is partly added.
		17	3. Memory information is revised.
			Figure 3.1 Memory Map is partly revised.
		18	Table 4.1 SFR Information(1) is partly revised.
		19	Table 4.2 SFR Information(2) is partly added.
		23	Table 5.1 Absolute Maximum Ratings information is revised.
		26	Table 5.4 Flash Memory Version Electrical Characteristics is added.
			Table 5.5 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics is added.
		28	Table 5.7 Electrical Characteristics(1) is partly deleted.
		29	Table 5.8 Electrical Characteristics (2) is partly revised.
		33	Table 5.23 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.
		34	Table 5.24 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.
		40	Table 5.25 Electrical Characteristics (1) is partly deleted.
		41	Table 5.26 Electrical Characteristics (2) is partly revised.
		45	Table 5.41 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.
		46	Table 5.42 Memory Expansion and Microprocessor Modes NOTES 3 is partly revised.

R	REVISION H	ISTOF	RY	M16C/30P Group Datasheet		
Rev.	Date			Description		
Nev.	Date	Page		Summary		
1.20	Oct 17, 2006	1	Note is pa	artly deleted.		
		2	Table 1.1	Performance Outline of M16C/30P Group is partly added.		
		4	Table 1.2	Product List is partly revised.		
		5	Figure 1.2	2 Type No., Memory Size, and Package is added.		
		7		Product Code of One Time Flash version, Flash Memory ver-		
		47		ROM-less version for M16C/30P is partly added.		
		17	•	Memory Map is partly added.		
		19	Table 4.2	SFR Information (2) is partly added.		
		23	Table 5.1	Absolute Maximum Ratings is partly added.		
		27	Table 5.6 One Time Flash Version Electrical Characteristics and Table 5.7 One Time Flash Version Program Voltage and Read Operation Voltage Characteristics is added.			
		30	Table 5.10	D Electrical Characteristics (2) is partly added.		
		42	Table 5.28	8 Electrical Characteristics (2) is partly added.		
1.21	Nov 02 2006	7	Table 1.4 Product Code of One Time Flash version, Flash Memory version, and ROM-less version for M16C/30P is partly revised.			
1.22	Mar 30, 2007	4	Table 1.2	Product List (1) is partly revised.		
		5	Table 1.3	Product List (2) is partly revised.		
		19	Table 4.2	SFR Information (2) is partly revised.		

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